

## MAX20446B

# Automotive 6-Channel Backlight Driver with Boost/SEPIC Controller, Hybrid Dimming and I<sup>2</sup>C Interface

### General Description

The MAX20446B is a 6-channel backlight driver with boost controller for automotive displays. The integrated current outputs can sink up to 130mA LED current each. The device accepts a wide 4.5V to 36V input voltage range and withstands automotive load-dump events.

The internal current-mode-switching DC-DC controller supports boost or SEPIC topologies, and operates in the 400kHz to 2.2MHz frequency range. Integrated spread spectrum helps reduce EMI. An adaptive output-voltage-control scheme minimizes power dissipation in the LED current-sink paths.

The device features I<sup>2</sup>C-controlled pulse-width-modulation (PWM) dimming and hybrid dimming. In either case, the minimum pulse width is 500ns. Optional phase-shifted dimming of the strings is incorporated for lower EMI.

Comprehensive diagnostic information is also available through the I<sup>2</sup>C interface.

The device is available in a 24-pin TQFN package and operates over the -40 to +125°C temperature range.

### Applications

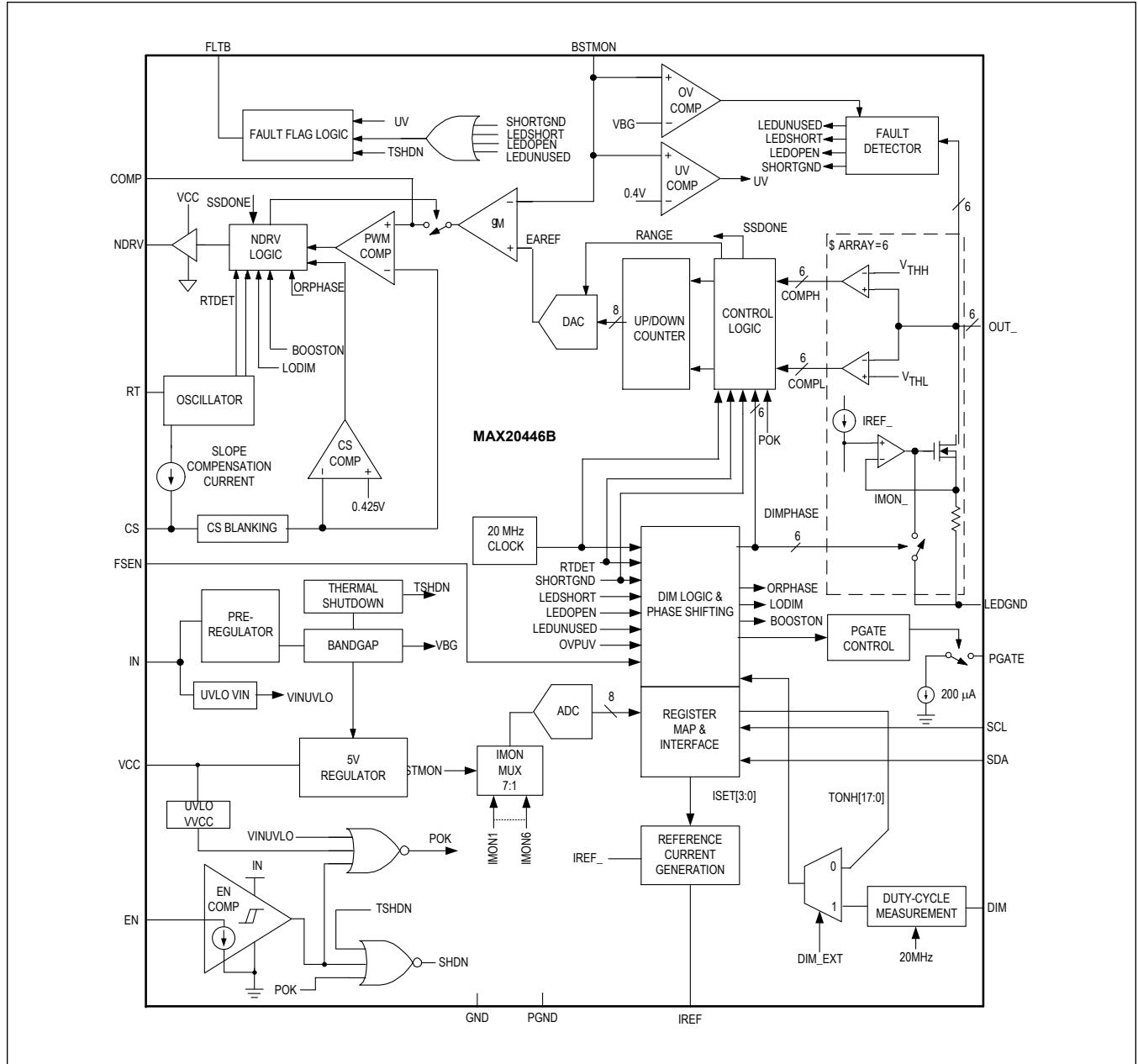
- Infotainment Displays
- Central Information Displays
- Instrument Clusters

### Benefits and Features

- Wide-Voltage-Range Operation
  - Operates Down to 4V Supply After Startup
  - Survives Load Dump Up to 52V
- High Integration
  - Complete 6-Channel Solution Including Boost Controller
  - I<sup>2</sup>C Control for Minimum Parts Count
- Robust and Low EMI
  - Spread-Spectrum Oscillator
  - Phase Shifting
  - 400kHz to 2.2MHz Switching-Frequency Range
  - Fail-Safe Operation Mode Using the FSEN Pin
- Versatile Dimming Scheme Allows Hybrid or PWM-Only Dimming Using DIM Input or I<sup>2</sup>C
  - Dimming Ratio > 10000:1 Using Hybrid Dimming
  - Dimming Ratio of 10000:1 at 200Hz Using PWM Dimming
- Complete Diagnostics
  - LED Open/Short Detection and Protection
  - Boost Output Undervoltage and Overvoltage
  - Boost Voltage
  - Individual String LED Current
  - Thermal Shutdown
- Compact (4mm x 4mm) 24-Pin TQFN Package

**Ordering Information appears at end of datasheet.**

Simplified Block Diagram



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## Absolute Maximum Ratings

IN, EN, OUT_, BSTMON, PGATE to GND .....	-0.3V to +52V	Continuous Power Dissipation Multilayer Board (derate 27.8mW/°C above +70°C) .....	2.857W
PGND, LEDGND to GND .....	-0.3V to +0.3V	ESDHB .....	-2kV to +2kV
V <sub>CC</sub> to GND .....	-0.3V to maximum of (+6, V <sub>IN</sub> + 0.3)V	ESDMM .....	-200V to +200V
FLTB, SCL, SDA, DIM to GND .....	-0.3V to +6V	Operating Temperature Range .....	-40°C to +125°C
CS, RT, COMP, NDRV, IREF, FSEN to GND .....	-0.3V to V <sub>CC</sub> + 0.3V	Junction Temperature Range .....	-40°C to +150°C
NDRV Peak Current (< 100ns) .....	-5A to +5A	Storage Temperature Range .....	-65°C to +150°C
NDRV Continuous Current .....	-100mA to +100mA	Lead Temperature (soldering, 10s) .....	+300°C
OUT1-6 Continuous Current .....	-100mA to +150mA		

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## Package Information

### TQFN

Package Code	T2444+4C
Outline Number	<a href="#">21-0139</a>
Land Pattern Number	<a href="#">90-0022</a>
<b>Thermal Resistance, Single-Layer Board:</b>	
Junction to Ambient ( $\theta_{JA}$ )	48°C/W
Junction to Case ( $\theta_{JC}$ )	3°C/W
<b>Thermal Resistance, Four-Layer Board:</b>	
Junction to Ambient ( $\theta_{JA}$ )	36°C/W
Junction to Case ( $\theta_{JC}$ )	3°C/W

### TQFN-SW

Package Code	T2444Y+4C
Outline Number	<a href="#">21-100290</a>
Land Pattern Number	<a href="#">90-0022</a>
<b>Thermal Resistance, Four-Layer Board:</b>	
Junction to Ambient ( $\theta_{JA}$ )	41.3°C/W
Junction to Case ( $\theta_{JC}$ )	3.44°C/W

For the latest package outline information and land patterns (footprints), go to [www.maximintegrated.com/packages](http://www.maximintegrated.com/packages). Note that a "+", "#", or "-" in the package code indicates RoHS status only. Package drawings may show a different suffix character, but the drawing pertains to the package regardless of RoHS status.

Package thermal resistances were obtained using the method described in JEDEC specification JESD51-7, using a four-layer board. For detailed information on package thermal considerations, refer to [www.maximintegrated.com/thermal-tutorial](http://www.maximintegrated.com/thermal-tutorial).

## Electrical Characteristics

(V<sub>IN</sub> = 12V, R<sub>RT</sub> = 76.8k $\Omega$ , C<sub>VCC</sub> = 1 $\mu$ F, T<sub>A</sub> = T<sub>J</sub> = -40°C to +125°C, unless otherwise noted., (V<sub>IN</sub> = 12V, R<sub>RT</sub> = 76.8k $\Omega$ , C<sub>VCC</sub> = 1 $\mu$ F, T<sub>A</sub> = T<sub>J</sub> = -40°C to +125°C, unless otherwise noted. Limits are 100% tested at T<sub>A</sub> = +25°C. Limits over the operating temperature range and relevant supply voltage range are guaranteed by design and characterization.))

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
<b>POWER INPUT</b>						
Input Operating Range			4.5		36	V

**Electrical Characteristics (continued)**

( $V_{IN} = 12V$ ,  $R_{RT} = 76.8k\Omega$ ,  $C_{VCC} = 1\mu F$ ,  $T_A = T_J = -40^\circ C$  to  $+125^\circ C$ , unless otherwise noted., ( $V_{IN} = 12V$ ,  $R_{RT} = 76.8k\Omega$ ,  $C_{VCC} = 1\mu F$ ,  $T_A = T_J = -40^\circ C$  to  $+125^\circ C$ , unless otherwise noted. Limits are 100% tested at  $T_A = +25^\circ C$ . Limits over the operating temperature range and relevant supply voltage range are guaranteed by design and characterization.))

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Input Voltage Range After Startup			4.2		36	V
Input Operating Range		IN pin connected to $V_{CC}$	4.5		5.5	V
Quiescent Supply Current		$V_{DIM} = 5V$ , $V_{BSTMON} = 1.3V$ , OUT1–OUT6 unconnected		10	15	mA
Standby Supply Current		$V_{IN} = 12V$ , $V_{EN} = 0V$		0.1	1	$\mu A$
Undervoltage Lockout, Rising			3.8	4.15	4.45	V
Undervoltage Lockout, Falling			3.1	3.7	4	V
Startup Delay		From EN high to I <sup>2</sup> C ready		1.2	1.8	ms
<b>V<sub>CC</sub> REGULATOR</b>						
$V_{CC}$ Output Voltage		$5.75V < V_{IN} < 36V$ ; $I_{VCC} = 1mA$ to $10mA$	4.75	5	5.25	V
Dropout Voltage		$V_{IN} = 4.5V$ , $I_{VCC} = 5mA$			0.2	V
Short-Circuit Current Limit		$V_{CC}$ shorted to GND		60		mA
$V_{CC}$ Undervoltage-Lockout Threshold, Rising			4.05	4.2	4.35	V
$V_{CC}$ Undervoltage-Lockout Threshold, Falling			3.75	3.9	4.04	V
<b>RT OSCILLATOR</b>						
Switching-Frequency Range	$f_{SW}$	Frequency dithering disabled	360		2420	kHz
Maximum Duty Cycle		$f_{SW} = 400kHz$	90	94.5	98.5	%
		$f_{SW} = 2200kHz$	86	90.5	95	
Oscillator Frequency Accuracy		$f_{SW} = 400kHz$ to $2200kHz$ , frequency dither disabled	-10		+10	%
Frequency Dither	SS	SSL bit = 1		$\pm 3$		%
RT Output Voltage	$V_{RT}$	$R_{RT} = 76.8k\Omega$ or $R_{RT} = 13.3k\Omega$	1.2	1.25	1.3	V
Sync Rising Threshold			3			V
Sync Frequency Duty-Cycle Range				50		%
Sync Frequency Range			$1.16 \times f_{SW}$		$1.5 \times f_{SW}$	kHz
<b>MOSFET DRIVER</b>						
NDRV On-Resistance, High Side		NDRV sinking 30mA		1.5	3	$\Omega$
NDRV On-Resistance, Low Side		NDRV sourcing 30mA		0.8	1.6	$\Omega$



**Electrical Characteristics (continued)**

( $V_{IN} = 12V$ ,  $R_{RT} = 76.8k\Omega$ ,  $C_{VCC} = 1\mu F$ ,  $T_A = T_J = -40^\circ C$  to  $+125^\circ C$ , unless otherwise noted., ( $V_{IN} = 12V$ ,  $R_{RT} = 76.8k\Omega$ ,  $C_{VCC} = 1\mu F$ ,  $T_A = T_J = -40^\circ C$  to  $+125^\circ C$ , unless otherwise noted. Limits are 100% tested at  $T_A = +25^\circ C$ . Limits over the operating temperature range and relevant supply voltage range are guaranteed by design and characterization.))

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
NDRV Rise Time		$C_{LOAD} = 1nF$		8		ns
NDRV Fall Time		$C_{LOAD} = 1nF$		8		ns
<b>SLOPE COMPENSATION</b>						
Peak Slope-Compensation Current-Ramp Magnitude		Current ramp added to CS	42	50	58	$\mu A$
<b>CURRENT-SENSE COMPARATOR</b>						
Current-Limit Threshold	$V_{CL\_MAX}$	Includes internal slope-ramp magnitude, $V_{CL} = V_{CS} + \text{slope-compensation voltage}$	390	420	450	mV
<b>ERROR AMPLIFIER</b>						
OUT_ Regulation High Threshold		$V_{OUT\_falling}$	0.95	1.03	1.1	V
OUT_ Regulation Low Threshold		$V_{OUT\_rising}$	0.7	0.78	0.85	V
Transconductance			500	700	880	$\mu S$
COMP Sink Current		$V_{COMP} = 2V$	200	480	800	$\mu A$
COMP Source Current		$V_{COMP} = 1V$	200	480	800	$\mu A$
<b>LED CURRENT SINKS</b>						
IREF Voltage	$V_{IREF}$	$R_{IREF} = 49.9k\Omega$	1.225	1.25	1.275	V
OUT_ Output Current		120mA setting	116	120	124.5	mA
		100mA setting	96	100	104	
		50mA setting	49	50.6	52.2	
Channel-to-Channel Matching		$I_{OUT\_} = 120mA$	-2		+2	%
		$I_{OUT\_} = 50mA$	-2.5		+2.5	
Total OUT_ Leakage Current to IN	$I_{OUTLEAK}$	$V_{OUT\_} = 48V$ , $V_{DIM} = 0V$ , all OUT_ pins shorted together		8	12	$\mu A$
OUT_ Current Rise Time		10% to 90% $I_{OUT\_}$		150		ns
OUT_ Current Fall Time		90% to 10% $I_{OUT\_}$		50		ns
DIM Sampling Frequency				20		MHz
<b>LOGIC INPUT AND OUTPUTS</b>						
EN Input Logic-High			2.1			V
EN Input Logic-Low					0.8	V
EN Input Current		$V_{EN} = 5V$		3	5	$\mu A$
DIM, SDA, SCL Input Logic-High			2.1			V
DIM, SDA, SCL Input Logic-Low					0.8	V

**Electrical Characteristics (continued)**

( $V_{IN} = 12V$ ,  $R_{RT} = 76.8k\Omega$ ,  $C_{VCC} = 1\mu F$ ,  $T_A = T_J = -40^\circ C$  to  $+125^\circ C$ , unless otherwise noted., ( $V_{IN} = 12V$ ,  $R_{RT} = 76.8k\Omega$ ,  $C_{VCC} = 1\mu F$ ,  $T_A = T_J = -40^\circ C$  to  $+125^\circ C$ , unless otherwise noted. Limits are 100% tested at  $T_A = +25^\circ C$ . Limits over the operating temperature range and relevant supply voltage range are guaranteed by design and characterization.))

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
DIM Input Pullup Current				5		$\mu A$
FSEN Input Voltage Threshold High		FSEN rising	2.2			V
FSEN Input Voltage Threshold Logic-Low	$V_{FSENIL}$	FSEN falling			1.8	V
FSEN Input Current	$I_{FSEN}$	$V_{FSEN} = 1V$		15		$\mu A$
SDA, FLTB Output Low Voltage		Sinking 3mA			0.4	V
FLTB Output Leakage Current		$V_{FLTB} = 5.5V$	-1		+1	$\mu A$
<b>OVERVOLTAGE AND UNDERVOLTAGE PROTECTION</b>						
BSTMON Overvoltage Trip Threshold		BSTMON rising	1.18	1.23	1.28	V
BSTMON Hysteresis				70		mV
BSTMON Input Bias Current		$0V < V_{BSTMON} < 1.3V$	-500		500	nA
BSTMON Undervoltage Detection Threshold		BSTMON falling, PGATE latched off	0.4	0.43	0.46	V
Boost Undervoltage Blanking Time		After ENA is written to '1', FAST_SS = 0	47.5	52	56.2	ms
BSTMON Undervoltage Detection Delay		BSTMON falling	4	10	18	$\mu s$
PGATE Pulldown Current			180	210	245	$\mu A$
PGATE Start Delay		Delay between PGATE going low and boost converter starting		2	2.2	ms
PGATE Leakage Current		$V_{PGATE} = 12V$ , $V_{EN} = 0V$		0.1	1	$\mu A$
<b>LED FAULT DETECTION</b>						
LED Short-Detection Threshold		SLDET[1:0] = 0x01	2.8	3	3.25	V
		SLDET[1:0] = 0x10	5.6	6	6.4	
		SLDET[1:0] = 0x11	7.5	8	8.5	
Short-Detection Comparator Delay				9		$\mu s$
OUT_ Check LED Source Current			50	60	70	$\mu A$
OUT_ Short-to-GND Detection Threshold		Before boost converter startup	250	300	365	mV
OUT_ Unused Detection Threshold			1.15	1.25	1.35	V

**Electrical Characteristics (continued)**

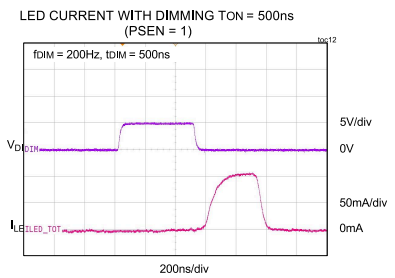
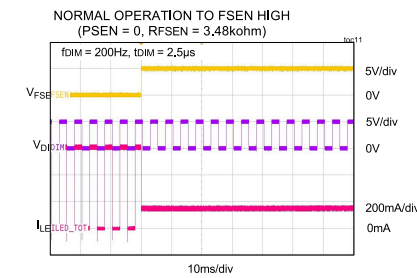
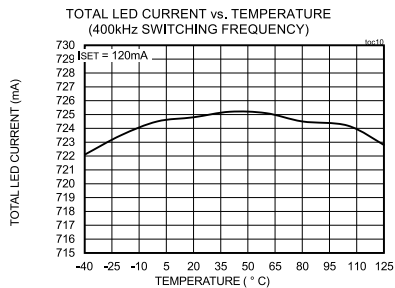
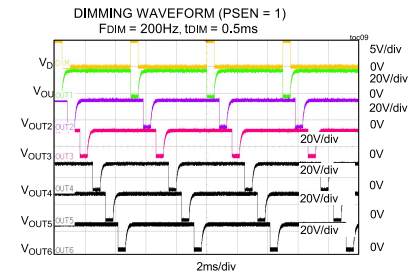
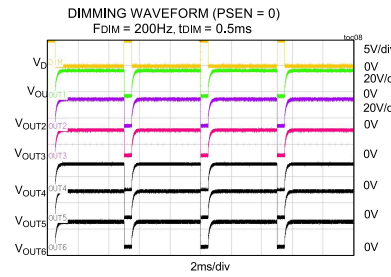
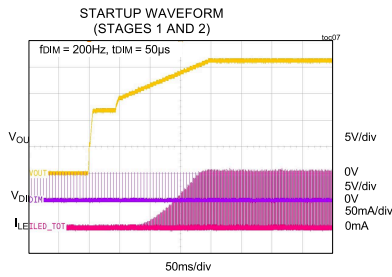
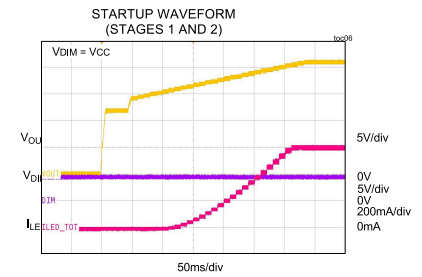
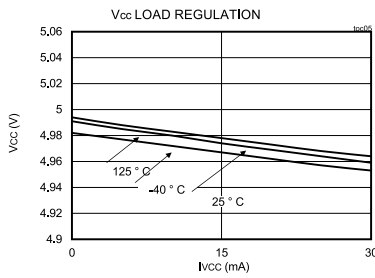
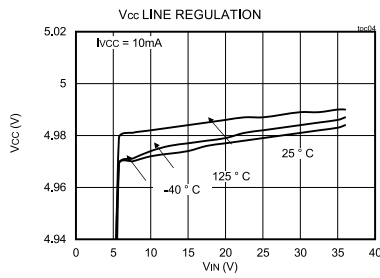
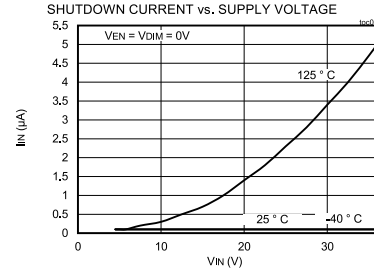
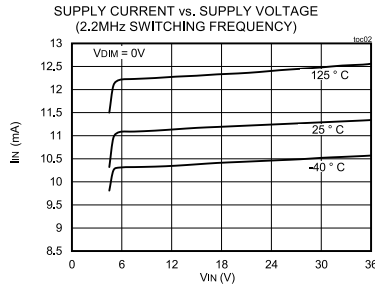
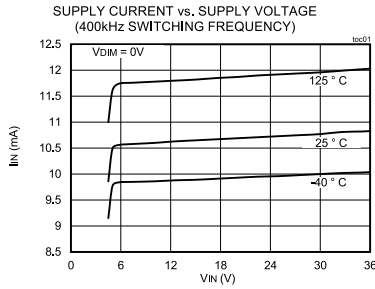
( $V_{IN} = 12V$ ,  $R_{RT} = 76.8k\Omega$ ,  $C_{VCC} = 1\mu F$ ,  $T_A = T_J = -40^\circ C$  to  $+125^\circ C$ , unless otherwise noted., ( $V_{IN} = 12V$ ,  $R_{RT} = 76.8k\Omega$ ,  $C_{VCC} = 1\mu F$ ,  $T_A = T_J = -40^\circ C$  to  $+125^\circ C$ , unless otherwise noted. Limits are 100% tested at  $T_A = +25^\circ C$ . Limits over the operating temperature range and relevant supply voltage range are guaranteed by design and characterization.))

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
OUT_ Open-LED Detection Threshold		During operation	250	300	365	mV
<b>ANALOG-TO-DIGITAL CONVERTER</b>						
ADC Measurement Resolution				8		Bits
Total Measurement Error, Current		$I_{OUT\_} = 120mA$	-7		+7.5	mA
Total Measurement Error, Voltage		$V_{BSTMON} = 1V$	-50		+70	mV
ADC Gain Error		$I_{OUT\_} = 120mA$	-4		+6	%
ADC Offset Error		$I_{OUT\_} = 120mA$	-3		+5	LSB
Measurement Resolution, Current				0.5		mA
Measurement Resolution, Voltage				5.1		mV
<b>THERMAL SHUTDOWN</b>						
Thermal Warning				125		$^\circ C$
Thermal-Shutdown Threshold				165		$^\circ C$
Thermal-Shutdown Hysteresis				15		$^\circ C$
<b>I<sup>2</sup>C INTERFACE</b>						
Serial-Clock Frequency	$f_{SCL}$				400	kHz
Bus-Free Time Between STOP and START Condition	$t_{BUF}$		1.3			$\mu s$
START Condition Setup Time	$t_{SU:STA}$		0.6			$\mu s$
START Condition Hold Time	$t_{HD:STA}$		0.6			$\mu s$
STOP Condition Setup Time	$t_{SU:STO}$		0.6			$\mu s$
Clock Low Period	$t_{LOW}$		1.3			$\mu s$
Clock High Period	$t_{HIGH}$		0.6			$\mu s$
Data Setup Time	$t_{SU:DAT}$		100			ns
Data Hold Time	$t_{HD:DAT}$	Measured from 50% point on SCL falling edge to SDA edge	0			$\mu s$
Pulse Width of Spike Suppressed	$t_{SP}$			50		ns

**Note 1:** Limits are 100% tested at  $T_A = +25^\circ C$ . Limits over the operating temperature range and relevant supply voltage range are guaranteed by design and characterization.

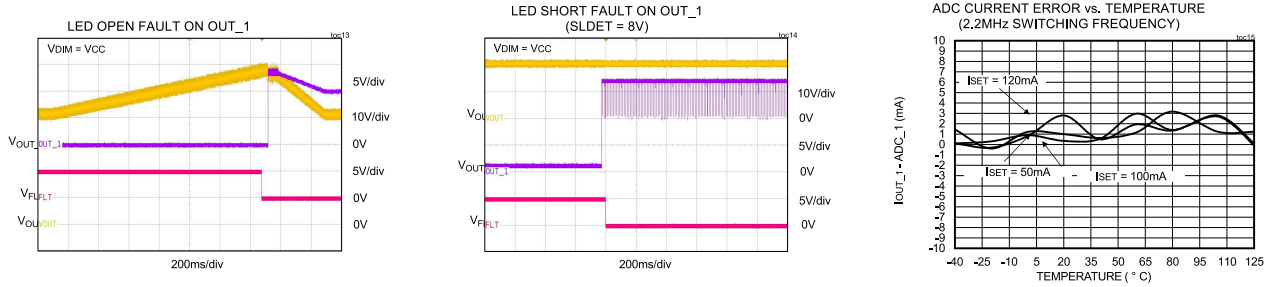
Typical Operating Characteristics

((V<sub>IN</sub> = V<sub>EN</sub> = +12V, 6x6 LED load at 100mA, T<sub>A</sub> = +25°C, unless otherwise noted.))



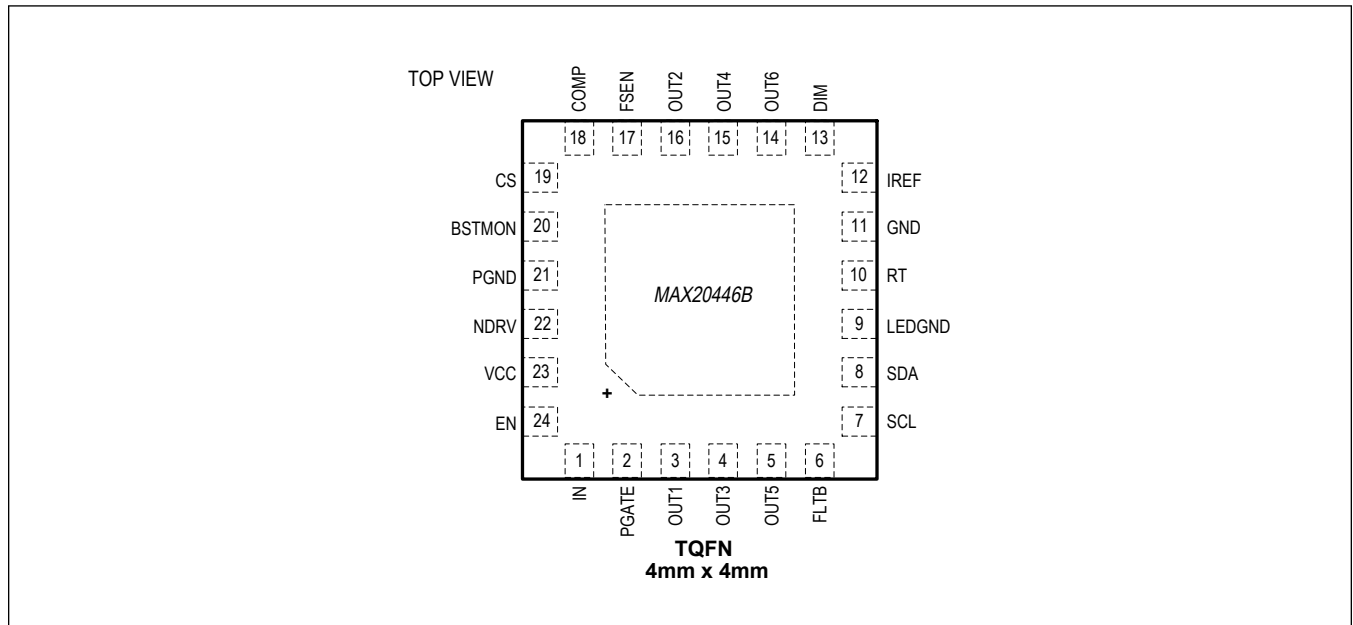
Typical Operating Characteristics (continued)

((V<sub>IN</sub> = V<sub>EN</sub> = +12V, 6x6 LED load at 100mA, T<sub>A</sub> = +25°C, unless otherwise noted.))



Pin Configuration

MAX20446B



Pin Description

PIN	NAME	FUNCTION
1	IN	Bias Supply Input. Connect a 4.5V to 36V supply to IN. Bypass IN to GND with a 2.2µF ceramic capacitor.
2	PGATE	Gate Connection for External Series pMOSFET
3	OUT1	LED String Cathode Connection 1. OUT1 is the open-drain output of the linear current sink that controls the current through the LED string connected to OUT1. OUT1 sinks up to 120mA.
4	OUT3	LED String Cathode Connection 3. OUT3 is the open-drain output of the linear current sink that controls the current through the LED string connected to OUT3. OUT3 sinks up to 120mA.

## Pin Description (continued)

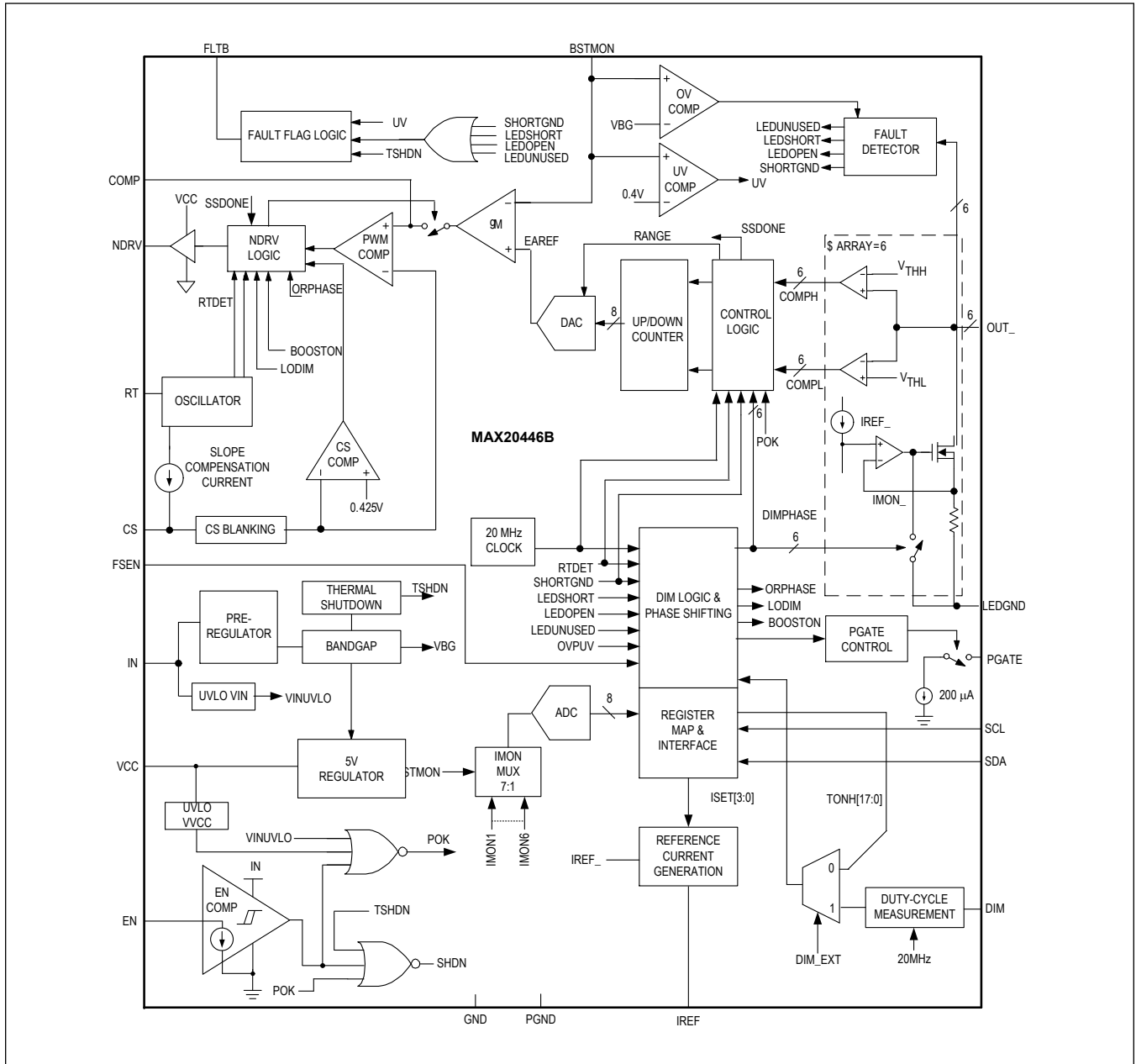
PIN	NAME	FUNCTION
5	OUT5	LED String Cathode Connection 5. OUT5 is the open-drain output of the linear current sink that controls the current through the LED string connected to OUT5. OUT5 sinks up to 120mA.
6	FLTB	Open-Drain Fault Output. FLTB asserts low when any diagnostic bit (that is not masked) is asserted. See the <i>Fault Protection</i> section for more details. Connect a pullup resistor from FLTB to V <sub>CC</sub> .
7	SCL	I <sup>2</sup> C Clock Input. Connect a pullup resistor from SCL to the logic supply.
8	SDA	I <sup>2</sup> C Data I/O Pin. Connect a pullup resistor from SDA to the logic supply.
9	LEDGND	LED Ground. LEDGND is the return path connection for the linear current sinks. Connect GND, LEDGND, and PGND at a single point.
10	RT	Oscillator Timing Resistor Connection. Connect a timing resistor (R <sub>RT</sub> ) from RT to GND to program the switching frequency. In addition, connect a 100pF capacitor from RT to GND. To synchronize the switching frequency with an external clock, apply an AC-coupled external clock at RT. When the oscillator is synchronized with the external clock, spread spectrum is disabled.
11	GND	Signal Ground. GND is the current return path connection for the low-noise analog signals. Connect GND, LEDGND, and PGND at a single point.
12	IREF	LED Current Reference Input. Connect a resistor (R <sub>IREF</sub> = 49.9kΩ) from IREF to GND to set the current reference according to the formula $IREF = 1.250/R_{IREF}$ .
13	DIM	PWM Dimming Input. Apply a PWM signal to DIM for LED dimming control unless I <sup>2</sup> C dimming is used. Connect DIM to V <sub>CC</sub> if dimming control is not used (100% brightness). Connect DIM to GND if dimming is to be controlled through I <sup>2</sup> C.
14	OUT6	LED String Cathode Connection 6. OUT6 is the open-drain output of the linear current sink that controls the current through the LED string connected to OUT6. OUT6 sinks up to 120mA.
15	OUT4	LED String Cathode Connection 4. OUT4 is the open-drain output of the linear current sink that controls the current through the LED string connected to OUT4. OUT4 sinks up to 120mA.
16	OUT2	LED String Cathode Connection 2. OUT2 is the open-drain output of the linear current sink that controls the current through the LED string connected to OUT2. OUT2 sinks up to 120mA.
17	FSEN	Fail-Safe Enable Pin. When FSEN is taken high, the boost converter is enabled and the outputs (OUT1–OUT6) are enabled at 100% duty cycle, independent of all register settings. Connect a resistor from FSEN to GND to set the LED current; FSEN sets both the LED current (when FSEN is active) and the I <sup>2</sup> C address (see the <i>MAX20446 FSEN Pin Function</i> section). If the FSEN function is not needed, connect the pin directly to GND.
18	COMP	Switching-Converter Compensation Input. Connect the compensation network from COMP to GND for current-mode control (see the <i>Feedback Compensation</i> section for details).
19	CS	Current-Sense Input. CS is the current-sense input for the switching regulator. A sense resistor connected from the source of the external power MOSFET to PGND sets the switching current limit. A resistor connected between the source of the power MOSFET and CS sets the slope-compensation ramp rate (see the <i>Slope Compensation and Current-Sense Resistor</i> section).
20	BSTMON	Overvoltage Threshold-Adjust Input. Connect a resistor-divider from the switching converter output to BSTMON and GND. The OVP comparator reference is internally set to 1.23V.
21	PGND	Power Ground. PGND is the switching-current return-path connection. Connect GND, LEDGND, and PGND at a single point.
22	NDRV	Switching nMOSFET Gate-Driver Output. Connect NDRV to the gate of the external switching-power MOSFET. Typically, a small resistor (1Ω to 22Ω) is inserted between the NDRV output and nMOSFET gate to decrease the slew rate of the gate driver and reduce the switching noise.
23	VCC	5V Regulator Output. Bypass V <sub>CC</sub> to GND with a minimum of 1μF ceramic capacitor with 22nF in parallel placed as close as possible to the pin.

## Pin Description (continued)

PIN	NAME	FUNCTION
24	EN	Enable Input. Connect EN to ground to shut down the device. Connect EN to logic-high or IN for normal operation. EN has an internal clamp at 3.9V. When EN is above this voltage, an input current of $(V_{EN} - 3.9V)/1.2M\Omega$ will flow.
-	EP	Exposed Pad. Connect EP to a large-area contiguous copper-ground plane for effective power dissipation. Do not use as the main IC ground connection. EP <b>must</b> be connected to GND.

Functional Diagrams

MAX20446B





## Detailed Description

The MAX20446B high-efficiency HB LED driver integrates all the necessary features to implement a high-performance backlight driver to power LEDs in medium-to-large-sized displays for automotive, as well as general, applications. The device provides load-dump voltage protection up to 52V in automotive applications and incorporates a DC-DC controller with peak current-mode control to implement a boost or a SEPIC-type switched-mode power supply and a 6-channel LED driver with 45mA to 130mA constant-current sink capability per channel.

### Enable

The internal regulator and I<sup>2</sup>C interface are enabled when the EN pin is high if the IN pin voltage is above its undervoltage lockout. To shut down the device, drive EN low so the current consumption is reduced to 1μA (max).

### Undervoltage Lockout

The device features two undervoltage lockouts (UVLOs) that monitor the input voltage at IN and the output of the internal LDO regulator at V<sub>CC</sub>. The device turns on when EN is taken high if both IN and V<sub>CC</sub> are higher than their respective UVLO thresholds.

### Current-Mode DC-DC Controller

The device has a constant-frequency, current-mode controller designed to drive the LEDs in a boost, SEPIC, or coupled-inductor buck-boost configuration. The device features multiloop control to regulate the peak current in the inductor, as well as the voltage across the LED current sinks to minimize power dissipation.

The switching frequency can be programmed over the 400kHz to 2.2MHz range using a resistor connected from RT to GND.

Internal slope compensation is provided to compensate for subharmonic oscillations that occur at above 50% duty cycles in continuous-conduction mode.

The internal MOSFET is turned on at the beginning of every switching cycle. The inductor current ramps up linearly until it is turned off at the peak current level set by the feedback loop. The peak inductor current is sensed from the voltage across the current-sense resistor (R<sub>CS</sub>), connected from the source of the external MOSFET to ground.

The device features leading-edge blanking to suppress the internal MOSFET switching noise. A PWM comparator compares the current-sense voltage plus the slope-compensation signal with the output of the transconductance error amplifier. The controller turns off the MOSFET when the voltage at CS exceeds the error amplifier's output voltage, which is also the voltage on the COMP pin. This process repeats every switching cycle to achieve peak current-mode control.

In addition to the peak current-mode-control loop, the device has two other feedback loops for control. The converter output voltage is sensed through the BSTMON input, which goes to the inverting input of the error amplifier. The other feedback comes from the OUT\_ current sinks. This loop controls the headroom of the current sinks to minimize total power dissipation while still ensuring accurate LED current matching. Each current sink has a window comparator with a low threshold of 0.78V and a high threshold of 1.03V. The outputs of these comparators control an up/down counter. The up/down counter is updated on every falling edge of the DIM input and drives an 8-bit DAC that sets the reference to the error amplifier. When dimming is set to 100%, the counter is updated at intervals of 10ms.

### 8-Bit Digital-to-Analog Converter

The error amplifier's reference input is controlled with an 8-bit digital-to-analog converter (DAC). The DAC output ramps up slowly during startup to implement a soft-start function (see the *Startup Sequence* section). During normal operation, the DAC output range is limited to 0.6V to 1.25V. Because the DAC output is limited to no less than 0.6V during normal operation, the overvoltage threshold for the output should be set to a value less than twice the minimum LED forward voltage. The DAC LSB determines the minimum step-in output voltage according to Equation 1.

#### Equation 1:

$$V_{\text{STEP\_MIN}} = V_{\text{DAC\_LSB}} \times \text{AOVP}$$

where:

V<sub>STEP\_MIN</sub> = Minimum output-voltage step

V<sub>DAC\_LSB</sub> = DAC least significant bit size (2.5mV)

A<sub>OVP</sub> = BSTMON resistor-divider gain

### FSEN Pin Function

The FSEN (fail-safe enable) pin can be used to enable the device in situations where I<sup>2</sup>C control is temporarily impossible or the interface has stopped functioning. When FSEN is taken high, the boost converter is turned on and the current sinks enabled. When FSEN returns low, the values programmed in the I<sup>2</sup>C registers are applied at the beginning of the next dimming cycle.

The OUT\_ current when FSEN is high is set by a resistor from FSEN to GND according to Table 1.

**Table 1. FSEN Pin Function**

FSEN RESISTOR VALUE (kΩ)	OUT_ CURRENT (mA)	MAX20446BATGA I <sup>2</sup> C ADDRESS	MAX20446BATG I <sup>2</sup> C ADDRESS
0	Fail-safe disabled	0x61	0x63
3.48	25	0x61	0x63
7.15	25	0x67	0x6B
12	50	0x61	0x63
18.7	50	0x67	0x6B
27.4	75	0x61	0x63
39	75	0x67	0x6B
59	100	0x61	0x63
84.5	100	0x67	0x6B

The resistor value is read at power-up; therefore, the set OUT\_ current value and I<sup>2</sup>C address cannot be changed after power-up.

If FSEN is not used, connect the pin to GND, unless an I<sup>2</sup>C address other than the default is desired.

### Dimming

Dimming can be performed either using an external PWM signal applied to the DIM pin or by programming the desired dimming level through I<sup>2</sup>C.

When using the DIM pin as an input, set the DIM\_EXT bit in the IMODE register (0x03) to 1 (this is also the default value). The signal on the DIM pin is sampled with a 20MHz internal clock.

When using internal dimming, write up to 18 bits to the TON\_[17:0] bits. The value to be written is calculated using the following formula:  $TON = t_{ON}/50ns$ , where  $t_{ON}$  is the desired on-time. If a value is written that corresponds to an on-time less than 500ns ( $\leq 0x09$ ), the corresponding OUT\_ stays on for 500ns. To set zero current in any channel, write all the corresponding TON bits to 0.

### Hybrid Dimming

In hybrid dimming mode, the external LEDs are dimmed by first reducing their current as the dimming duty-cycle decreases from 100% (see [Figure 1](#)). At the crossover level set by the HDIM[1:0] bits, dimming transitions to PWM in which the LED current is chopped. To select hybrid dimming, set the HDIM bit in the IMODE register and select the desired crossover level between analog and PWM dimming using the HDIM\_THR[1:0] bits in the same register (see [Figure 1](#)). Depending on the DIM\_EXT bit, one of the following occurs:

- If DIM\_EXT = 1, the device measures the duty-cycle on the DIM pin and translates it into a combined LED current value and PWM setting.
- If DIM\_EXT = 0, the device takes the concatenated 18-bit value from the TONH\_:TONL\_:TON\_LSB registers and

translates it into a combined LED current value and PWM setting.

**Note:** When hybrid dimming is used with an internal dimming setting (e.g., DIM\_EXT = 0) only the value in the TONH\_:TONL\_ registers is used. It is not possible to have individual dimming settings for each of the channels in this mode, but the TONH:TONL settings for all the channels must be non-zero.

In summary, there are four possible dimming modes:

- External PWM dimming
- Internal PWM dimming with the pulse width set through I<sup>2</sup>C and the PWM frequency generated internally.
- External hybrid dimming with a PWM signal applied to the DIM pin. In this mode the pulsed current on the OUT\_ pins follows the DIM frequency.
- Internal hybrid dimming with the dimming ratio set through I<sup>2</sup>C and the PWM frequency generated internally.

Figure 2 illustrates the difference between standard and hybrid dimming with phase shifting enabled.

**Hybrid Dimming Operation**

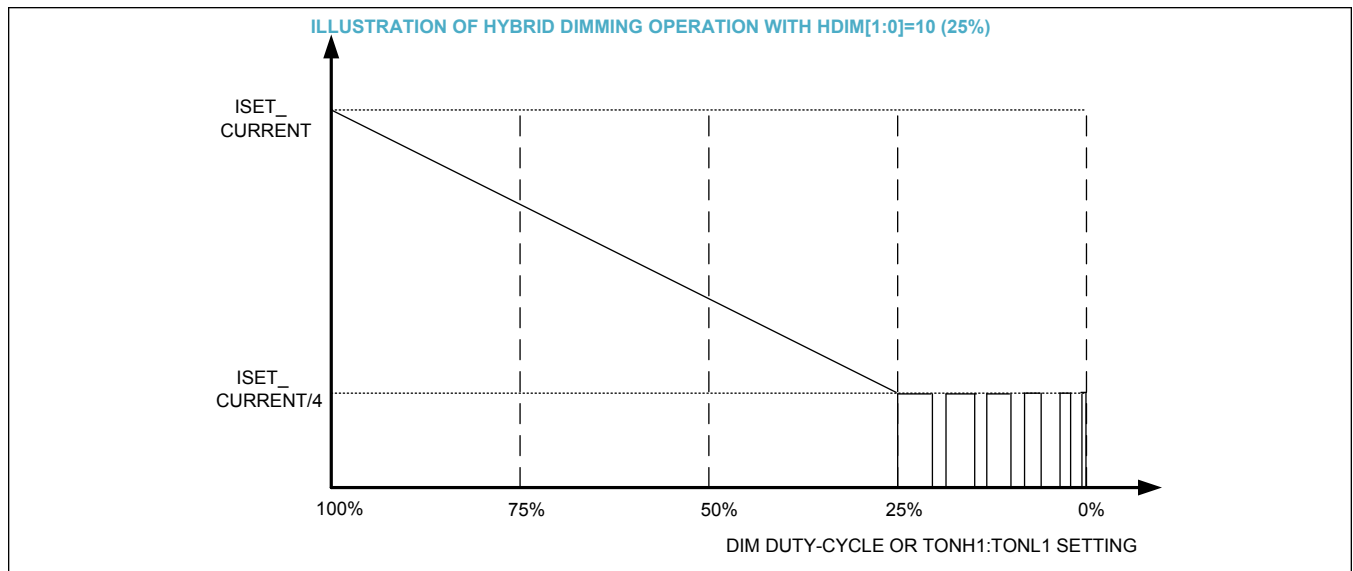


Figure 1. Hybrid Dimming Operation

### Hybrid Dimming Operation Modes

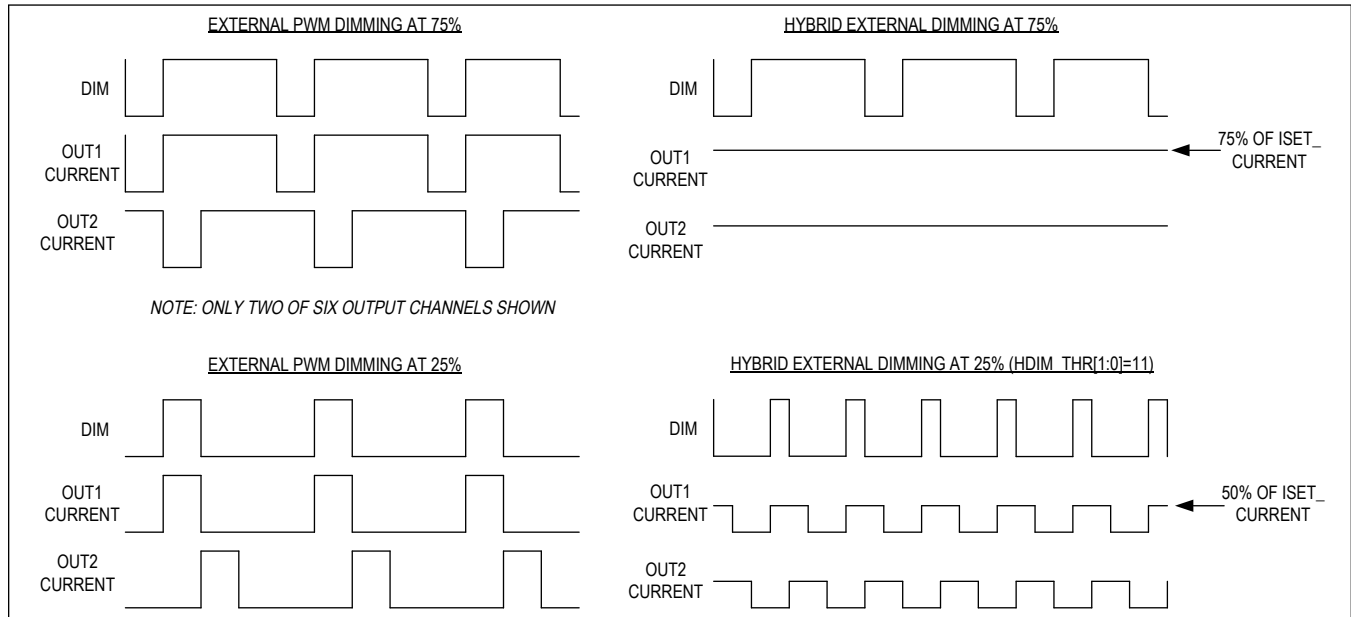


Figure 2. Hybrid Dimming Operation Modes

### Low-Dimming Mode

The device operation changes at very narrow dimming pulses to ensure a consistent dimming response of the LEDs. If the dimming on-time (either of the DIM input or of the value in the PWM\_ bits, depending on which is selected) is lower than 50 $\mu$ s (typ), the device enters low-dimming mode. In this state, the converter switches continuously and the LED short detection is disabled. When the DIM input is greater than 51 $\mu$ s (typ), the device goes back into normal operation, enabling the short-LED detection and switching the power MOSFET only when the effective dimming signal is high. OUT\_ current monitoring does not operate in low-dim mode, although the BSTMON voltage can still be measured.

When the device is used in I<sup>2</sup>C mode with internal dimming, some channels may be in low-dim mode while others may not. If any channel is in low-dim mode, the boost converter runs continuously.

### Phase-Shift Dimming

When the PSEN bit in the ISET register (0x02) is set, phase shifting of the LED strings is enabled. The device automatically sets the phase shift between strings to 60, 72, 90, 120, or 180 degrees, depending on the number of strings enabled.

### Disabling Individual Strings

To disable an unused LED string, connect the unused OUT\_ to ground through a 12k $\Omega$  resistor, or set the corresponding DIS\_ bit to 1 in the DISABLE (0x13) register. During startup, the device sources 60 $\mu$ A (typ) current through the OUT\_ pins and measures the corresponding voltage. For the string to be properly disabled, the OUT\_ voltage should measure between 350mV and 1.15V during this check. 350mV is the maximum threshold for the OUT\_ short-to-ground check and 1.15V is the minimum unused string-detection threshold.

**Note:** When disabling unused strings, start by disabling the highest numbered current sinks first (e.g., if two strings need to be disabled, disable OUT6 and OUT5. Do not disable any two strings at random). During normal operation, strings can be selectively turned off by changing the corresponding PWM setting to 0. This is only possible when internal dimming is used (not when using the DIM input pin).

## Startup Sequence

When the EN pin is taken high (assuming the IN voltage is above its undervoltage-lockout value), the internal regulator and the interface are turned on and the device checks the OUT\_ channels. If any of the OUT\_ pins are detected as shorted to GND, the boost converter will not start (to avoid possible damage) and the corresponding OUTSG bit(s) are set. The device also detects and disconnects any unused current-sink channels that are connected to GND through a 12kΩ resistor. Alternatively, when using the I<sup>2</sup>C interface, individual channels can be disabled using the DIS4:1 bits. The total duration of this phase of the startup is 2ms (max). After this phase, the I<sup>2</sup>C interface can be used and the device registers written. Finally, the ENA bit is set to 1 to enable the boost and subsequently the OUT\_ current sinks. When the ENA bit is set high, the startup sequence occurs in three stages (see the Stage 1, Stage 2, and Stage 3 sections).

### Stage 1

Once the ENA bit is high, the controller begins the soft-start of the boost. First, the driver of the external pMOSFET is turned on. A constant current of 200μA (typ) then flows into the PGATE pin of the device. This current flows into the external gate-source resistor and pulls down the gate of the external pMOSFET and turns it on. An external gate-source capacitor can be used to control the turn-on time of the external pMOSFET.

After the external pMOSFET is turned on and a 2ms timeout expires, Stage 2 of the startup begins (see the Stage 2 section).

### Stage 2

After the checks in Stage 1 have been performed, the converter starts switching and the output begins to ramp. The DAC reference to the error amplifier is stepped up 1 bit at a time until it reaches 600mV (or 1.1V if fast soft start is enabled). This stage duration is fixed at approximately 50ms (typ) (or 25ms when DIS\_FASTSS is set to 0). The BSTMON pin is then monitored, and if the voltage at the BSTMON pin is less than 500mV (typ), FLTB is asserted low, the power converter is turned off, the external pMOSFET is turned off, and they all remain off until the ENA bit is toggled (see the Stage 3 section).

### Stage 3

The third stage begins once Stage 2 is complete and the DIM input goes high (with DIM\_EXT = 1), or internal dimming is enabled by setting a PWM value greater than 0 on any of the channels. During Stage 3, the output of the converter is adjusted until the minimum OUT\_ voltage falls within 0.68V (typ) and 0.93V (typ) comparator limits. The output adjustment is again controlled by the DAC, which provides the reference for the error amplifier. The DAC output is updated on each rising edge of the DIM input pin (or internal dimming signal). If the DIM input (or the internal dimming signal when DIM\_EXT = 1) is at 100% duty cycle (DIM = high), the DAC output is updated once every 10ms.

The total soft-start time can be calculated using Equation 2.

#### Equation 2:

$$t_{SS} = 52\text{ms} + \frac{(V_{LED} + 0.91) - (0.6 \times A_{OVP})}{f_{DIM} \times 0.01 \times A_{OVP}}$$

where:

SS = Total soft-start time

52ms = Fixed Stage 1 + Stage 2 duration (27ms when DIS\_FASTSS = 0)

V<sub>LED</sub> = Total forward voltage of the LED strings

0.91V = Midpoint of the window comparator

0.6 = Voltage on BSTMON after Stage 2 (use 1.1 when DIS\_FASTSS = 0)

f<sub>DIM</sub> = Dimming frequency (use 100Hz for f<sub>DIM</sub> when input duty cycle is 100%)

0.01V = 4 times the 2.5mV LSB of the DAC

A<sub>OVP</sub> = Gain of the BSTMON resistor-divider or 1 + R6/R7

After the soft-start period, a fault is detected whenever the BSTMON pin falls below 430mV (typ). When this occurs, the

power converter is latched off and PGATE goes high. Cycling the ENA bit or the supply is required to start up again once the fault condition has been removed.

**Figure 3: Boost Startup**

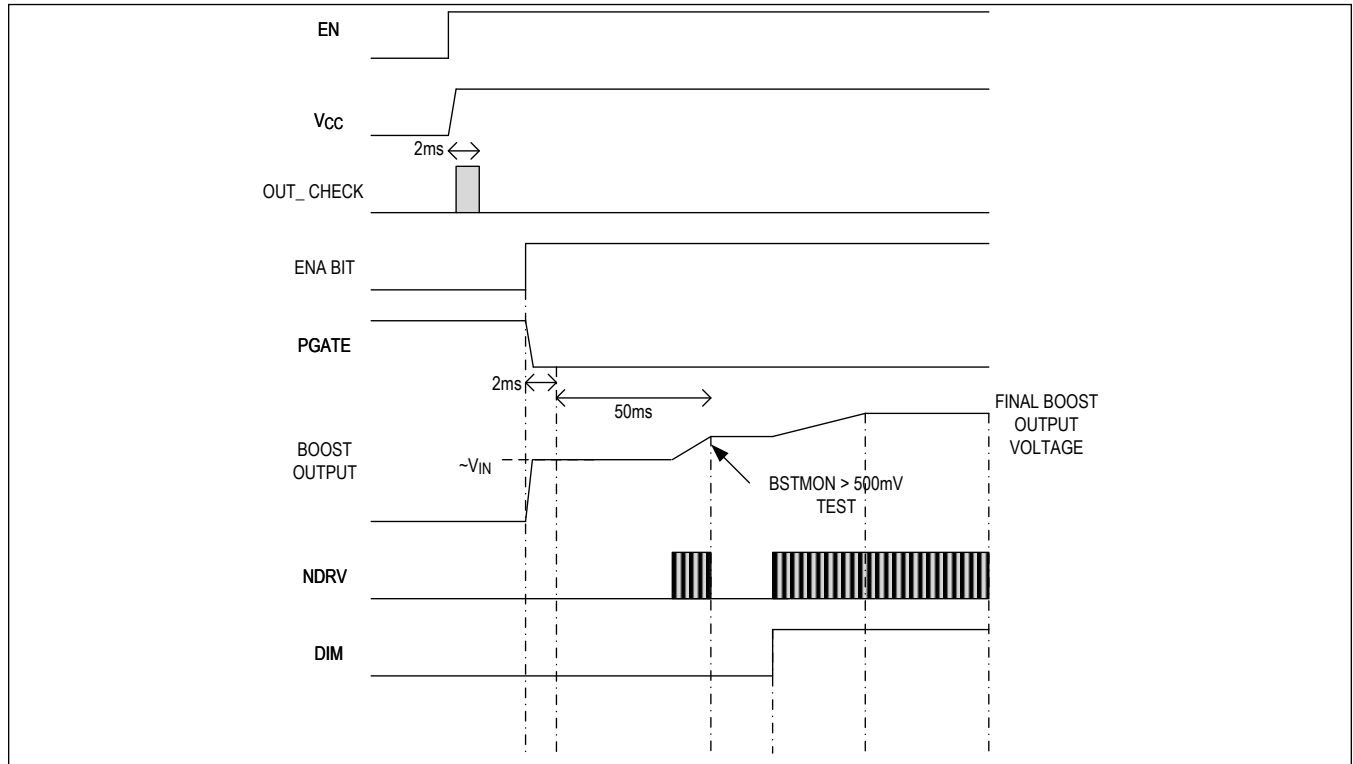


Figure 3. Boost Startup with DIS\_FASTSS = 1

**Oscillator Frequency/External Synchronization**

The internal oscillator frequency is programmable between 400kHz and 2.2MHz using a timing resistor (R<sub>RT</sub>) connected from the RT pin to GND. Use Equation 3 to calculate the value of R<sub>RT</sub> for the desired switching frequency (f<sub>SW</sub>).

**Equation 3:**

$$R_{RT} = \frac{29260 + (2200 - f_{SW}) \times 0.81}{f_{SW}}$$

where f<sub>SW</sub> is in kHz and R<sub>RT</sub> is in kΩ.

Synchronize the oscillator with an external clock by AC-coupling the external clock to the RT input. The value of the capacitor used for AC-coupling is C<sub>SYNC</sub> = 10pF and the duty cycle of the external clock should be 50%.

**Spread-Spectrum Mode**

The device includes a spread-spectrum mode that reduces peak electromagnetic interference (EMI) at the switching frequency and its harmonics.

The spread spectrum uses a pseudorandom dithering technique where the switching frequency is varied in the range of 97% (or 94% when the SSL bit is 1) of the programmed switching frequency, to 103% (or 106% when the SSL bit is 1) of the programmed switching frequency set through the external resistor from RT to GND. When spread spectrum is used, the total energy at the fundamental and each harmonic is spread over a wider bandwidth, reducing the energy peak.

Spread spectrum is disabled if external synchronization is used. Optionally, spread spectrum can be disabled by setting the SS\_OFF bit in the SETTING register to 1. The amount of spread spectrum can also be varied between ±3% and ±6% using the SSL bit in the same register.

### 5V LDO Regulator (V<sub>CC</sub>)

The internal LDO regulator converts the input voltage at IN to a 5V output voltage at V<sub>CC</sub>. The LDO regulator supplies up to 50mA current to provide power to internal control circuitry and the gate driver. Bypass V<sub>CC</sub> to GND, with a minimum of 1µF (+22nF in parallel) ceramic capacitor, as close as possible to the device.

### LED Current Control

The full-scale sink current for the outputs OUT1–OUT6 is set using the four bits ISET3:0 in register 0x01. See the *ISET* (0x02) section to find the correct bit value for the desired current. When PWM dimming is used, the current in the OUT\_ channels switches between zero and the full-scale sink current at the set duty cycle.

When hybrid dimming is used, the sink current in OUT1–OUT6 is reduced linearly from the full-scale value until the level set by HDIM\_THR[1:0] is reached; dimming at lower levels is then accomplished using PWM (see [Figure 1](#)).

If 130mA current is desired, the resistor on IREF should be changed to 45.3kΩ.

### Fault Protection

Fault protection in the device includes cycle-by-cycle current limiting using the PWM controller, DC-DC converter output undervoltage protection, output overvoltage protection, open-LED detection, short-LED detection and protection, and overtemperature shutdown. An open-drain fault flag output (FLT\_B) goes low when an open-LED string is detected, a short-LED string is detected, during an output undervoltage, or during thermal shutdown. FLT\_B is cleared when the fault condition is removed during thermal shutdown and shorted LED detection. FLT\_B is latched low for an open LED and can be reset by cycling device power. The thermal-shutdown threshold is +165°C and has +15°C hysteresis.

### Open-LED Management and Overvoltage Protection

On power-up, the device performs a soft-start of the boost converter. After soft-start, the device detects open-LED and disconnects any strings with an open LED from the internal minimum OUT\_ voltage detector. This keeps the DC-DC converter output voltage within safe limits and maintains high efficiency. The current in strings that have been detected open is not measured and reads as zero.

During normal operation, the DC-DC converter output-regulation loop uses the minimum OUT\_ voltage as the feedback input. If any LED string is open, the voltage at the opened OUT\_ goes to V<sub>LEDGND</sub>. The DC-DC converter output voltage then increases to the overvoltage-protection threshold set by the voltage-divider network connected between the converter output, the BSTMON input, and GND. The overvoltage-protection threshold at the DC-DC converter output is determined using Equation 4.

#### Equation 4:

$$V_{OUT\_BSTMON} = 1.23 \times \left(1 + \frac{R6}{R7}\right)$$

where 1.23 (typ) is the overvoltage threshold on BSTMON (see [Functional Diagrams](#)). Select V<sub>OUT\_BSTMON</sub> according to Equation 5.

#### Equation 5:

$$1.1 \times (V_{LED\_MAX} + 1.1) < V_{OUT\_BSTMON} < 2 \times (V_{LED\_MIN} + 0.7)$$

where:

V<sub>LED\_MAX</sub> = Maximum expected LED string voltage, and

V<sub>LED\_MIN</sub> = Minimum expected LED string voltage.

Select R6 and R7 such that the voltage at OUT\_ does not exceed the [Absolute Maximum Ratings](#). As soon as the DC-DC converter output reaches the overvoltage-protection threshold, the internal MOSFET is switched off.

The overvoltage threshold should be set less than twice the minimum LED voltage to ensure proper operation; the BSTMON minimum regulation point is 600mV (typ). Connect a 12kΩ resistor between OUT\_ and LEDGND for each unused channel to avoid overvoltage triggering at startup. When an open-LED overvoltage condition occurs, FLTB is latched low. Any current-sink output with  $V_{OUT\_} < 300\text{mV}$  (typ) is disconnected from the minimum voltage detector.

### Short-LED Detection

The device checks for shorted LEDs before the current in any channel is turned on. A shorted LED is detected at OUT\_ if the condition in Equation 6 is met.

#### Equation 6:

$$V_{OUT\_} > RSDT$$

where:

RSDT = Programmable short-LED detection threshold set by the SLDET[2:0] bits in the SETTING (0x12) register.

If a short is detected on any of the strings, the affected LED strings are disconnected and the FLTB output flag asserts until the device detects that the shorts are removed. Disable short-LED detection by setting SLDET[2:0] to 0. Short-LED detection is disabled in low-dimming mode. In external dimming mode with the DIM input connected continuously high, the OUT\_ pins are periodically scanned to detect shorted LEDs. The scan frequency is 100Hz.

Similarly when DIM\_EXT = 0 and internal dimming is being used, shorted LEDs are still detected by periodically scanning the OUT\_ states.

### Thermal Warning/Shutdown

The device includes thermal protection that operates at a temperature of 165°C. When the thermal-shutdown temperature is reached, the device is immediately disabled and begins to cool. When the junction temperature falls by 15°C, the device is re-enabled with the same settings as before (the boost converter performs a soft-start). When a thermal shutdown occurs, the FLTB pin goes low and the OT bit, if read through I<sup>2</sup>C, is set to 1.

A thermal-warning bit (OTW) implemented in register 0x1F, indicates when the junction temperature has exceeded 125°C. The OTWMASK bit in register 0x1E is used to control whether or not an active OTW bit causes the FLTB pin to go low.

### Analog-to-Digital Converter

The analog-to-digital converter (ADC) is used to measure the current in each of the strings and the voltage on the BSTMON pin. A conversion cycle is started by setting the CONVERT bit to 1. At the end of the cycle, the CONVERT bit is reset to 0 to indicate a complete cycle and the IOUT1–OUT6 and BSTMON registers contain the updated values. The full-scale value of the current measurement is 127.5mA. Values higher than 127.5mA read as full-scale or 0xFF. Current measurements are not performed on channels that are in low-dim mode; before performing a conversion, this can be checked by reading the LoDIM\_ bits. If a conversion is attempted on a channel that is in low-dim mode, the current value returned will be 0x00. The duration of a complete conversion depends on whether or not phase shifting is enabled. With phase shifting enabled, a complete conversion can take up to two dimming cycles (worst case). With phase shifting disabled, one dimming cycle is the worst-case latency (the conversion is initiated at the beginning of a DIM cycle and is concluded < 50μs later).

### I<sup>2</sup>C Interface

The IC features an I<sup>2</sup>C, 2-wire serial interface consisting of a serial-data line (SDA) and a serial-clock line (SCL). SDA and SCL facilitate communication between the device and the master at clock rates up to 400kHz. The master, typically a microcontroller, generates SCL and initiates data transfer on the bus.

The slave address is chosen by connecting the FSEN pin to GND via a resistor, the value of which determines the I<sup>2</sup>C address (see also *FSEN Pin Function*). [Table 2](#) shows the possible I<sup>2</sup>C addresses.



**Table 2. I<sup>2</sup>C Address Options**

DEVICE	FSEN	DEVICE ADDRESS								WRITE ADDRESS	READ ADDRESS	7-BIT ADDRESS
		A6	A5	A4	A3	A2	A1	A0				
MAX20446BATG	0, 3.48k, 12k, 27.4k, 59k	1	1	0	0	0	0	1	0xC6	0xC7	0x63	
MAX20446BATG	7.15k, 18.7k, 39k, 84.5k	1	1	0	0	1	1	1	0xD6	0xD7	0x6B	
MAX20446BATGA	0, 3.48k, 12k, 27.4k, 59k	1	1	0	0	0	1	1	0xC2	0xC3	0x61	
MAX20446BATGA	7.15k, 18.7k, 39k, 84.5k	1	1	0	1	0	1	1	0xCE	0xCF	0x67	

## Register Map

## MAX20446B

ADDRESS	NAME	MSB							LSB
<b>I2C</b>									
0x00	<a href="#">Dev_ID[7:0]</a>	Device_ID[7:0]							
0x01	<a href="#">Rev_ID[7:0]</a>	-	-	LoDIM6	LoDIM5	Revision_ID[3:0]			
0x02	<a href="#">ISET[7:0]</a>	-	CONVE RT	ENA	PSEN	ISET[3:0]			
0x03	<a href="#">IMODE[7:0]</a>	LoDIM4	LoDIM3	LoDIM2	LoDIM1	DIM_EX T	HDIM	HDIM_THR[1:0]	
0x04	<a href="#">TONH1[7:0]</a>	PWM1[17:10]							
0x05	<a href="#">TONL1[7:0]</a>	PWM1[9:2]							
0x06	<a href="#">TONH2[7:0]</a>	PWM2[17:10]							
0x07	<a href="#">TONL2[7:0]</a>	PWM2[9:2]							
0x08	<a href="#">TONH3[7:0]</a>	PWM3[17:10]							
0x09	<a href="#">TONL3[7:0]</a>	PWM3[9:2]							
0x0A	<a href="#">TONH4[7:0]</a>	PWM4[17:10]							
0x0B	<a href="#">TONL4[7:0]</a>	PWM4[9:2]							
0x0C	<a href="#">TON1-4LSB[7:0]</a>	PWM4[1:0]		PWM3[1:0]		PWM2[1:0]		PWM1[1:0]	
0x0D	<a href="#">TONH5[7:0]</a>	PWM5[17:10]							
0x0E	<a href="#">TONL5[7:0]</a>	PWM5[9:2]							
0x0F	<a href="#">TONH6[7:0]</a>	PWM6[17:10]							
0x10	<a href="#">TONL6[7:0]</a>	PWM6[9:2]							
0x11	<a href="#">TON5-6LSB[7:0]</a>	-	-	-	-	PWM6[1:0]		PWM5[1:0]	
0x12	<a href="#">SETTING[7:0]</a>	-	FPWM[2:0]			SS_OFF	SSL	SLDET[1:0]	
0x13	<a href="#">DISABLE[7:0]</a>	-	DIS_FAS TSS	DIS6	DIS5	DIS4	DIS3	DIS2	DIS1
0x14	<a href="#">BSTMON[7:0]</a>	VMON[7:0]							
0x15	<a href="#">IOUT1[7:0]</a>	IOUT1[7:0]							
0x16	<a href="#">IOUT2[7:0]</a>	IOUT2[7:0]							
0x17	<a href="#">IOUT3[7:0]</a>	IOUT3[7:0]							
0x18	<a href="#">IOUT4[7:0]</a>	IOUT4[7:0]							
0x19	<a href="#">IOUT5[7:0]</a>	IOUT5[7:0]							
0x1A	<a href="#">IOUT6[7:0]</a>	IOUT6[7:0]							
0x1B	<a href="#">OPEN[7:0]</a>	-	-	OUT6O	OUT5O	OUT4O	OUT3O	OUT2O	OUT1O
0x1C	<a href="#">SHORTGND[7:0]</a>	-	-	OUT6SG	OUT5SG	OUT4SG	OUT3SG	OUT2SG	OUT1SG
0x1D	<a href="#">SHORTED LED[7:0]</a>	-	-	OUT6SL	OUT5SL	OUT4SL	OUT3SL	OUT2SL	OUT1SL
0x1E	<a href="#">MASK[7:0]</a>	-	-	-	BSTUVM ASK	OMASK	SGMAS K	OTWMA SK	SLMASK
0x1F	<a href="#">DIAG[7:0]</a>	-	-	IREFOO R	BSTUV	BSTOV	HW_RS T	OTW	OT

## Register Details

Dev\_ID (0x00)

BIT	7	6	5	4	3	2	1	0
Field	Device_ID[7:0]							
Reset	0x6B							
Access Type	Read Only							
BITFIELD	BITS	DESCRIPTION			DECODE			
Device_ID	7:0				Device ID, reads 0x6B			

Rev\_ID (0x01)

BIT	7	6	5	4	3	2	1	0
Field	–	–	LoDIM6	LoDIM5	Revision_ID[3:0]			
Reset	–	–			0x1			
Access Type	–	–	Read Only	Read Only	Read Only			
BITFIELD	BITS		DESCRIPTION					
LoDIM6	5		When 1, indicates that channel 6 is in low-dim mode.					
LoDIM5	4		When 1, indicates that channel 5 is in low-dim mode.					
Revision_ID	3:0		Device revision ID					

ISET (0x02)

Boost slew rate and output-current setting.

BIT	7	6	5	4	3	2	1	0
Field	–	CONVERT	ENA	PSEN	ISET[3:0]			
Reset	–	0b0	0b0	0b1	0b1011			
Access Type	–	Write, Read	Write, Read	Write, Read	Write, Read			
BITFIELD	BITS		DESCRIPTION					
CONVERT	6		Write a 1 to this bit to start a conversion cycle of the ADC. When the cycle is finished this bit is automatically reset to indicate that data is ready.					
ENA	5		Table 3.					
			<b>ENA</b>	<b>ENABLE BIT</b>				
			0	Boost converter and LED outputs off				
			1	Boost converter and LED outputs on				
PSEN	4		When 0 phase-shifting is disabled. Default value 1.					

BITFIELD	BITS	DESCRIPTION																																																																																					
ISET	3:0	Table 4. LED Current Setting																																																																																					
		<table border="1"> <thead> <tr> <th>ISET3</th> <th>ISET2</th> <th>ISET1</th> <th>ISET0</th> <th>Current Setting</th> </tr> </thead> <tbody> <tr><td>0</td><td>0</td><td>0</td><td>0</td><td>45mA</td></tr> <tr><td>0</td><td>0</td><td>0</td><td>1</td><td>50mA</td></tr> <tr><td>0</td><td>0</td><td>1</td><td>0</td><td>55mA</td></tr> <tr><td>0</td><td>0</td><td>1</td><td>1</td><td>60mA</td></tr> <tr><td>0</td><td>1</td><td>0</td><td>0</td><td>65mA</td></tr> <tr><td>0</td><td>1</td><td>0</td><td>1</td><td>70mA</td></tr> <tr><td>0</td><td>1</td><td>1</td><td>0</td><td>75mA</td></tr> <tr><td>0</td><td>1</td><td>1</td><td>1</td><td>80mA</td></tr> <tr><td>1</td><td>0</td><td>0</td><td>0</td><td>85mA</td></tr> <tr><td>1</td><td>0</td><td>0</td><td>1</td><td>90mA</td></tr> <tr><td>1</td><td>0</td><td>1</td><td>0</td><td>95mA</td></tr> <tr><td>1</td><td>0</td><td>1</td><td>1</td><td>100mA*</td></tr> <tr><td>1</td><td>1</td><td>0</td><td>0</td><td>105mA</td></tr> <tr><td>1</td><td>1</td><td>0</td><td>1</td><td>110mA</td></tr> <tr><td>1</td><td>1</td><td>1</td><td>0</td><td>115mA</td></tr> <tr><td>1</td><td>1</td><td>1</td><td>1</td><td>120mA</td></tr> </tbody> </table>	ISET3	ISET2	ISET1	ISET0	Current Setting	0	0	0	0	45mA	0	0	0	1	50mA	0	0	1	0	55mA	0	0	1	1	60mA	0	1	0	0	65mA	0	1	0	1	70mA	0	1	1	0	75mA	0	1	1	1	80mA	1	0	0	0	85mA	1	0	0	1	90mA	1	0	1	0	95mA	1	0	1	1	100mA*	1	1	0	0	105mA	1	1	0	1	110mA	1	1	1	0	115mA	1	1	1	1	120mA
		ISET3	ISET2	ISET1	ISET0	Current Setting																																																																																	
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1	1	1	0	115mA																																																																																			
1	1	1	1	120mA																																																																																			
*default value																																																																																							

**IMODE (0x03)**

Phase-shift enable, individual string disable, analog dimming enable, and setting of crossover between analog/digital dimming (50%, 25%, 12.5%, 6.25%).

BIT	7	6	5	4	3	2	1	0
<b>Field</b>	LoDIM4	LoDIM3	LoDIM2	LoDIM1	DIM_EXT	HDIM	HDIM_THR[1:0]	
<b>Reset</b>	0x0	0x0	0x0	0x0	0b1	0b0	0b00	
<b>Access Type</b>	Read Only	Read Only	Read Only	Read Only	Write, Read	Write, Read	Write, Read	

BITFIELD	BITS	DESCRIPTION	DECODE
LoDIM4	7	When 1, indicates that channel 4 is in low-dim mode.	
LoDIM3	6	When 1, indicates that channel 3 is in low-dim mode.	
LoDIM2	5	When 1, indicates that channel 2 is in low-dim mode.	
LoDIM1	4	When 1, indicates that channel 1 is in low-dim mode.	
DIM_EXT	3	When 1, dimming through the DIM pin is enabled. When 0, dimming is controlled using the PWM_ registers. Default value is 1.	
HDIM	2	When 1, hybrid dimming is enabled. Default value 0.	When 1, hybrid dimming is enabled. Default value 0.

BITFIELD	BITS	DESCRIPTION	DECODE
HDIM_THR	1:0	Set hybrid dimming threshold. Default value is 6.25% (00).	

**TONH1 (0x04)**

On-time setting for channel 1 with 50ns resolution, high byte.

BIT	7	6	5	4	3	2	1	0
<b>Field</b>	PWM1[17:10]							
<b>Reset</b>	0b11111111							
<b>Access Type</b>	Write, Read							

BITFIELD	BITS	DESCRIPTION
PWM1	7:0	High byte of 16-bit PWM setting for channel 1.

**TONL1 (0x05)**

On-time setting for channel 1 with 50ns resolution, low byte.

BIT	7	6	5	4	3	2	1	0
<b>Field</b>	PWM1[9:2]							
<b>Reset</b>	0b11111111							
<b>Access Type</b>	Write, Read							

BITFIELD	BITS	DESCRIPTION
PWM1	7:0	Middle byte of 18-bit PWM setting for channel 1.

**TONH2 (0x06)**

On-time setting for channel 2 with 50ns resolution2, high byte

BIT	7	6	5	4	3	2	1	0
<b>Field</b>	PWM2[17:10]							
<b>Reset</b>	0b11111111							
<b>Access Type</b>	Write, Read							

BITFIELD	BITS	DESCRIPTION
PWM2	7:0	High byte of 16-bit PWM setting for channel 2.

**TONL2 (0x07)**

On-time setting for channel 2 with 50ns resolution, low byte.

BIT	7	6	5	4	3	2	1	0
<b>Field</b>	PWM2[9:2]							
<b>Reset</b>	0b11111111							
<b>Access Type</b>	Write, Read							

BITFIELD	BITS	DESCRIPTION
PWM2	7:0	Middle byte of 18-bit PWM setting for channel 2.

**TONH3 (0x08)**

On-time setting for channel 3 with 50ns resolution, high byte.

BIT	7	6	5	4	3	2	1	0
Field	PWM3[17:10]							
Reset	0b11111111							
Access Type	Write, Read							

BITFIELD	BITS	DESCRIPTION
PWM3	7:0	High byte of 16-bit PWM setting for channel 3.

**TONL3 (0x09)**

On-time setting for channel 3 with 50ns resolution, low byte.

BIT	7	6	5	4	3	2	1	0
Field	PWM3[9:2]							
Reset	0b11111111							
Access Type	Write, Read							

BITFIELD	BITS	DESCRIPTION
PWM3	7:0	Middle byte of 18-bit PWM setting for channel 3.

**TONH4 (0x0A)**

On-time setting for channel 4 with 50ns resolution, high byte.

BIT	7	6	5	4	3	2	1	0
Field	PWM4[17:10]							
Reset	0b11111111							
Access Type	Write, Read							

BITFIELD	BITS	DESCRIPTION
PWM4	7:0	High byte of 16-bit PWM setting for channel 4.

**TONL4 (0x0B)**

On-time setting for channel 4 with 50ns resolution, low byte.

BIT	7	6	5	4	3	2	1	0
Field	PWM4[9:2]							
Reset	0b11111111							
Access Type	Write, Read							

BITFIELD	BITS	DESCRIPTION
PWM4	7:0	Middle byte of 18-bit PWM setting for channel 4.

**TON1-4LSB (0x0C)**

BIT	7	6	5	4	3	2	1	0
Field	PWM4[1:0]		PWM3[1:0]		PWM2[1:0]		PWM1[1:0]	
Reset	0b11		0b11		0b11		0b11	
Access Type	Write, Read		Write, Read		Write, Read		Write, Read	

BITFIELD	BITS	DESCRIPTION
PWM4	7:6	2 least significant bits of 18-bit PWM setting for channel 4.
PWM3	5:4	2 least significant bits of 18-bit PWM setting for channel 3.
PWM2	3:2	2 least significant bits of 18-bit PWM setting for channel 2.
PWM1	1:0	2 least significant bits of 18-bit PWM setting for channel 1.

**TONH5 (0x0D)**

On-time setting for channel 5 with 50ns resolution, high byte.

BIT	7	6	5	4	3	2	1	0
Field	PWM5[17:10]							
Reset	0xFF							
Access Type	Write, Read							

BITFIELD	BITS	DESCRIPTION
PWM5	7:0	High byte of 16-bit PWM setting for channel 5.

**TONL5 (0x0E)**

On-time setting for channel 5 with 50ns resolution, low byte.

BIT	7	6	5	4	3	2	1	0
Field	PWM5[9:2]							
Reset	0b11111111							
Access Type	Write, Read							

BITFIELD	BITS	DESCRIPTION
PWM5	7:0	Middle byte of 18-bit PWM setting for channel 5.

**TONH6 (0x0F)**

On-time setting for channel 6 with 50ns resolution, high byte.

BIT	7	6	5	4	3	2	1	0
Field	PWM6[17:10]							
Reset	0b11111111							
Access Type	Write, Read							

BITFIELD	BITS	DESCRIPTION
PWM6	7:0	High byte of 16-bit PWM setting for channel 6.

**TONL6 (0x10)**

On-time setting for channel 6 with 50ns resolution, low byte.

BIT	7	6	5	4	3	2	1	0
Field	PWM6[9:2]							
Reset	0b11111111							
Access Type	Write, Read							

BITFIELD	BITS	DESCRIPTION
PWM6	7:0	Middle byte of 18-bit PWM setting for channel 6.

**TON5-6LSB (0x11)**

BIT	7	6	5	4	3	2	1	0
Field	–	–	–	–	PWM6[1:0]		PWM5[1:0]	
Reset	–	–	–	–	0b11		0b11	
Access Type	–	–	–	–	Write, Read		Write, Read	

BITFIELD	BITS	DESCRIPTION
PWM6	3:2	2 least significant bits of 18-bit PWM setting for channel 6.
PWM5	1:0	2 least significant bits of 18-bit PWM setting for channel 5.

**SETTING (0x12)**

External/internal dimming, DIM-frequency level for shorted-LED detection.

BIT	7	6	5	4	3	2	1	0
Field	–	FPWM[2:0]			SS_OFF	SSL	SLDET[1:0]	
Reset	–	0b001			0b0	0b0	000	
Access Type	–	Write, Read			Write, Read	Write, Read	Write, Read	

BITFIELD	BITS	DESCRIPTION
FPWM	6:4	These bits set the PWM frequency in internal PWM mode. When an external DIM signal is used, these bits set the fault-sampling frequency at 100% duty cycle.
SS_OFF	3	When 1 spread-spectrum switching is disabled. Default value 0.



BITFIELD	BITS	DESCRIPTION															
SSL	2	When spread-spectrum is enabled the SSL bit chooses the amount of spread: when 0 the spread is nominally ±6%, when 1 ±3%.															
SLDET	1:0	<table border="1"> <thead> <tr> <th>SLDET1</th> <th>SLDET0</th> <th>SETTING</th> </tr> </thead> <tbody> <tr> <td>0</td> <td>0</td> <td>Disabled</td> </tr> <tr> <td>0</td> <td>1</td> <td>3V</td> </tr> <tr> <td>1</td> <td>0</td> <td>6V</td> </tr> <tr> <td>1</td> <td>1</td> <td>8V</td> </tr> </tbody> </table>	SLDET1	SLDET0	SETTING	0	0	Disabled	0	1	3V	1	0	6V	1	1	8V
		SLDET1	SLDET0	SETTING													
		0	0	Disabled													
		0	1	3V													
		1	0	6V													
1	1	8V															
<b>Shorted-LED Threshold Setting:</b>																	

**DISABLE (0x13)**

BIT	7	6	5	4	3	2	1	0
Field	–	DIS_FASTSS	DIS6	DIS5	DIS4	DIS3	DIS2	DIS1
Reset	–	0x0	0b0	0b0	0b0	0b0	0b0	0b0
Access Type	–	Write, Read	Write, Read	Write, Read	Write, Read	Write, Read	Write, Read	Write, Read

BITFIELD	BITS	DESCRIPTION
DIS_FASTSS	6	Selects fast or slow boost soft-start. Set to 1 for slow soft-start.
DIS6	5	Set this bit to 1 to disable OUT6. This must be done before ENA is written to 1.
DIS5	4	Set this bit to 1 to disable OUT5. This must be done before ENA is written to 1.
DIS4	3	Set this bit to 1 to disable OUT4. This must be done before ENA is written to 1.
DIS3	2	Set this bit to 1 to disable OUT3. This must be done before ENA is written to 1.
DIS2	1	Set this bit to 1 to disable OUT2. This must be done before ENA is written to 1.
DIS1	0	Set this bit to 1 to disable OUT1. This must be done before ENA is written to 1.

**BSTMON (0x14)**

BSTMON pin voltage readback.

BIT	7	6	5	4	3	2	1	0
Field	VMON[7:0]							
Reset	0b00000000							
Access Type	Read Only							

BITFIELD	BITS	DESCRIPTION
VMON	7:0	Voltage on BSTMON. Full-scale = 2.5V.

**IOUT1 (0x15)**

OUT1 current readback.

<b>BIT</b>	<b>7</b>	<b>6</b>	<b>5</b>	<b>4</b>	<b>3</b>	<b>2</b>	<b>1</b>	<b>0</b>
<b>Field</b>	IOUT1[7:0]							
<b>Reset</b>	0b00000000							
<b>Access Type</b>	Read Only							

BITFIELD	BITS	DESCRIPTION												
IOUT1	7:0	Table 5. Output Current Measurement (IOUT1):												
		<table border="1"> <thead> <tr> <th>READOUT</th> <th>CURRENT (mA)</th> </tr> </thead> <tbody> <tr> <td>0x00</td> <td>0</td> </tr> <tr> <td>0x01</td> <td>0.5</td> </tr> <tr> <td>...</td> <td>...</td> </tr> <tr> <td>0xFE</td> <td>127</td> </tr> <tr> <td>0xFF</td> <td>127.5</td> </tr> </tbody> </table>	READOUT	CURRENT (mA)	0x00	0	0x01	0.5	...	...	0xFE	127	0xFF	127.5
		READOUT	CURRENT (mA)											
		0x00	0											
		0x01	0.5											
		...	...											
0xFE	127													
0xFF	127.5													

**IOUT2 (0x16)**

OUT2 current readback.

<b>BIT</b>	<b>7</b>	<b>6</b>	<b>5</b>	<b>4</b>	<b>3</b>	<b>2</b>	<b>1</b>	<b>0</b>
<b>Field</b>	IOUT2[7:0]							
<b>Reset</b>								
<b>Access Type</b>	Read Only							

BITFIELD	BITS	DESCRIPTION												
IOUT2	7:0	Output Current Measurement (IOUT2):												
		<table border="1"> <thead> <tr> <th>READOUT</th> <th>CURRENT (mA)</th> </tr> </thead> <tbody> <tr> <td>0x00</td> <td>0</td> </tr> <tr> <td>0x01</td> <td>0.5</td> </tr> <tr> <td>...</td> <td>...</td> </tr> <tr> <td>0xFE</td> <td>127</td> </tr> <tr> <td>0xFF</td> <td>127.5</td> </tr> </tbody> </table>	READOUT	CURRENT (mA)	0x00	0	0x01	0.5	...	...	0xFE	127	0xFF	127.5
		READOUT	CURRENT (mA)											
		0x00	0											
		0x01	0.5											
		...	...											
0xFE	127													
0xFF	127.5													

**IOUT3 (0x17)**

OUT3 current readback.

<b>BIT</b>	<b>7</b>	<b>6</b>	<b>5</b>	<b>4</b>	<b>3</b>	<b>2</b>	<b>1</b>	<b>0</b>
<b>Field</b>	IOUT3[7:0]							
<b>Reset</b>								
<b>Access Type</b>	Read Only							

BITFIELD	BITS	DESCRIPTION	
IOUT3	7:0	<b>Output Current Measurement (IOUT3):</b>	
		<b>READOUT</b>	<b>CURRENT (mA)</b>
		0x00	0
		0x01	0.5
		...	...
		0xFF	127.5

**IOUT4 (0x18)**

OUT4 current readback.

BIT	7	6	5	4	3	2	1	0
<b>Field</b>	IOUT4[7:0]							
<b>Reset</b>	0b00000000							
<b>Access Type</b>	Read Only							

BITFIELD	BITS	DESCRIPTION	
IOUT4	7:0	<b>Table 6. Output Current Measurement (IOUT4):</b>	
		<b>READOUT</b>	<b>CURRENT (mA)</b>
		0x00	0
		0x01	0.5
		...	...
		0xFF	127.5

**IOUT5 (0x19)**

OUT5 current readback.

BIT	7	6	5	4	3	2	1	0
<b>Field</b>	IOUT5[7:0]							
<b>Reset</b>	0b00000000							
<b>Access Type</b>	Read Only							

BITFIELD	BITS	DESCRIPTION	
IOUT5	7:0	<b>Table 7. Output Current Measurement (IOUT5):</b>	
		<b>READOUT</b>	<b>CURRENT (mA)</b>
		0x00	0
		0x01	0.5
		...	...
		0xFF	127.5

**IOUT6 (0x1A)**

OUT6 current readback.

BIT	7	6	5	4	3	2	1	0
Field	IOUT6[7:0]							
Reset	0b00000000							
Access Type	Read Only							

BITFIELD	BITS	DESCRIPTION												
IOUT6	7:0	Table 8. Output Current Measurement (IOUT6):												
		<table border="1"> <thead> <tr> <th>READOUT</th> <th>CURRENT (mA)</th> </tr> </thead> <tbody> <tr> <td>0x00</td> <td>0</td> </tr> <tr> <td>0x01</td> <td>0.5</td> </tr> <tr> <td>...</td> <td>...</td> </tr> <tr> <td>0xFE</td> <td>127</td> </tr> <tr> <td>0xFF</td> <td>127.5</td> </tr> </tbody> </table>	READOUT	CURRENT (mA)	0x00	0	0x01	0.5	...	...	0xFE	127	0xFF	127.5
		READOUT	CURRENT (mA)											
		0x00	0											
		0x01	0.5											
		...	...											
0xFE	127													
0xFF	127.5													

**OPEN (0x1B)**

Short-to-GND and open diagnostics.

BIT	7	6	5	4	3	2	1	0
Field	–	–	OUT6O	OUT5O	OUT4O	OUT3O	OUT2O	OUT1O
Reset	–	–	0x0	0b0	0b0	0b0	0b0	0b0
Access Type	–	–	Read Only	Read Only	Read Only	Read Only	Read Only	Read Only

BITFIELD	BITS	DESCRIPTION
OUT6O	5	If 1, an open has been detected on channel 6.
OUT5O	4	If 1, an open has been detected on channel 5.
OUT4O	3	If 1, an open has been detected on channel 4.
OUT3O	2	If 1, an open has been detected on channel 3.
OUT2O	1	If 1, an open has been detected on channel 2.
OUT1O	0	If 1, an open has been detected on channel 1.

**SHORTGND (0x1C)**

BIT	7	6	5	4	3	2	1	0
Field	–	–	OUT6SG	OUT5SG	OUT4SG	OUT3SG	OUT2SG	OUT1SG
Reset	–	–						
Access Type	–	–	Read Only	Read Only	Read Only	Read Only	Read Only	Read Only

BITFIELD	BITS	DESCRIPTION
OUT6SG	5	If 1, a short-to-ground has been detected on channel 6 at startup.
OUT5SG	4	If 1, a short-to-ground has been detected on channel 5 at startup.
OUT4SG	3	If 1, a short-to-ground has been detected on channel 4 at startup.

BITFIELD	BITS	DESCRIPTION
OUT3SG	2	If 1, a short-to-ground has been detected on channel 3 at startup.
OUT2SG	1	If 1, a short-to-ground has been detected on channel 2 at startup.
OUT1SG	0	If 1, a short-to-ground has been detected on channel 1 at startup.

**SHORTED LED (0x1D)**

Shorted-LED diagnostics.

BIT	7	6	5	4	3	2	1	0
Field	–	–	OUT6SL	OUT5SL	OUT4SL	OUT3SL	OUT2SL	OUT1SL
Reset	–	–	0b0	0b0	0b0	0b0	0b0	0b0
Access Type	–	–	Read Only	Read Only	Read Only	Read Only	Read Only	Read Only

BITFIELD	BITS	DESCRIPTION
OUT6SL	5	If 1, a shorted-LED condition has been detected on channel 6.
OUT5SL	4	If 1, a shorted-LED condition has been detected on channel 5.
OUT4SL	3	If 1, a shorted-LED condition has been detected on channel 4.
OUT3SL	2	If 1, a shorted-LED condition has been detected on channel 3.
OUT2SL	1	If 1, a shorted-LED condition has been detected on channel 2.
OUT1SL	0	If 1, a shorted-LED condition has been detected on channel 1.

**MASK (0x1E)**

Mask register for FLTB pin.

BIT	7	6	5	4	3	2	1	0
Field	–	–	–	BSTUVMASK	OMASK	SGMASK	OTWMASK	SLMASK
Reset	–	–	–	0b0	0b0	0b0	0b0	0b0
Access Type	–	–	–	Write, Read	Write, Read	Write, Read	Write, Read	Write, Read

BITFIELD	BITS	DESCRIPTION
BSTUVMASK	4	When 1 a boost fault (undervoltage or overvoltage) does not cause the FLT pin to assert low.
OMASK	3	When 1 an open-LED fault does not cause the FLT pin to assert low.
SGMASK	2	When 1 a short-to-ground LED fault does not cause the FLT pin to assert low.
OTWMASK	1	When 1 an over-temperature warning does not cause the FLT pin to assert low.
SLMASK	0	When 1 a shorted-LED fault does not cause the FLT pin to assert low.

**DIAG (0x1F)**

Boost state, over-temperature warning/shutdown.

BIT	7	6	5	4	3	2	1	0
Field	–	–	IREFOOR	BSTUV	BSTOV	HW_RST	OTW	OT
Reset	–	–	0b0	0b0	0b0	0b1		0b0
Access Type	–	–	Read Only	Read Only	Read Only	Read Only	Read Only	Read Only

BITFIELD	BITS	DESCRIPTION
IREFOOR	5	When 1, this bit indicates that the IREF current is out of range. This is probably due to an incorrect resistor value on IREF. In this condition, the IC stops operation.
BSTUV	4	If 1, an undervoltage has been detected on the boost output and the boost was disabled.
BSTOV	3	If 1, the boost converter is at its overvoltage limit.
HW_RST	2	If 1, the device has just emerged from a hardware reset (power-up). This bit is reset after the first read from this register.
OTW	1	If 1, the junction temperature of the device is over 125°C.
OT	0	If 1, the junction temperature of the device exceeded 165°C and the device was shut down.

## Applications Information

### DC-DC Converter

Three different converter topologies are possible with the DC-DC converter in the MAX20446B, which have the ground-referenced outputs necessary to use the constant-current sink drivers. If the LED string forward voltage is always greater than the input supply voltage range, use the boost converter topology. If the LED string forward voltage falls within the supply voltage range, use a buck-boost converter topology. The possible buck-boost topologies are SEPIC or a coupled-inductor buck-boost topology. The latter is basically a flyback converter with 1:1 turns ratio. 1:1-coupled inductors are available with tight coupling suitable for this application.

The boost-converter topology provides the highest efficiency among the above-mentioned topologies. The coupled-inductor topology has the advantage of not using a coupling capacitor, but does require tightly coupled windings to avoid additional snubber components. The SEPIC configuration requires two inductors (or a coupled inductor) and a coupling capacitor. Furthermore, the feedback-loop compensation for SEPIC becomes complex if the coupling capacitor is not large enough.

### Power-Circuit Design

First, select a converter topology based on the factors listed in the *DC-DC Converter* section. Determine the required input supply voltage range, the maximum voltage needed to drive the LED strings, including the minimum 0.85V across the constant LED current sink ( $V_{LED}$ ), and the total output current needed to drive the LED strings ( $I_{LED}$ ), as shown in Equation 7.

#### Equation 7:

$$I_{LED} = I_{STRING} \times N_{STRING}$$

where  $I_{STRING}$  is the current per string and  $N_{STRING}$  is the number of strings used.

Next, calculate the maximum duty cycle ( $D_{MAX}$ ) using Equations 8 and 9.

#### For boost configuration (Equation 8):

$$D_{MAX} = \frac{(V_{LED} + V_{D1} - V_{IN\_MIN})}{(V_{LED} + V_{D1} - V_{DS} - 0.3)}$$

#### For SEPIC and coupled-inductor buck-boost configurations (Equation 9):

$$D_{MAX} = \frac{V_{LED} + V_{D1}}{(V_{IN\_MIN} - V_{DS} - 0.3 + V_{LED} + V_{D1})}$$

where:

- $V_{D1}$  = Forward drop of the rectifier diode in volts (approximately 0.6V),
- $V_{IN\_MIN}$  = Minimum input supply voltage, and
- $V_{DS}$  = Drain-to-source voltage of the external MOSFET when it is on.

Select the switching frequency ( $f_{SW}$ ) depending on the space, noise, and efficiency constraints.

### Boost and Coupled-Inductor Configurations

In all three converter configurations, the average inductor current varies with the line voltage; the maximum average current occurs at the lowest line voltage. For the boost converter, the average inductor current is equal to the input current. Select the maximum peak-to-peak ripple on the inductor current ( $\Delta I_L$ ). The recommended maximum peak-to-peak ripple is 60% of the average inductor current, but lower and higher values for ripple are also acceptable.

Use the following equations (Equations 10, 11, and 12) to calculate the maximum average inductor current ( $I_{LAVG}$ ) and peak inductor current ( $I_{LP}$ ) in amperes.

#### Equation 10:

$$I_{LAVG} = \frac{I_{LED}}{(1 - D_{MAX})}$$

Allowing the peak-to-peak inductor ripple  $\Delta I_L$  to be  $\pm 30\%$  of the average inductor current:

**Equation 11:**

$$\Delta I_L = I_{LAVG} \times 0.3 \times 2$$

and:

$$I_{LP} = I_{LAVG} + \frac{\Delta I_L}{2}$$

Calculate the minimum inductance value ( $L_{MIN}$ ), in henries (H), with the inductor current ripple set to the maximum value:

**Equation 12:**

$$L_{MIN} = \frac{(V_{IN\_MIN} - V_{DS} - 0.3) \times D_{MAX}}{f_{SW} \times \Delta I_L}$$

Choose an inductor that has a minimum inductance greater than the calculated  $L_{MIN}$  and current rating greater than  $I_{LP}$ . The recommended saturation current limit of the selected inductor is 10% higher than the inductor peak current for boost configuration. For the coupled-inductor, the saturation limit of the inductor with only one winding conducting should be 10% higher than  $I_{LP}$ .

### SEPIC Configuration

Power-circuit design for the SEPIC configuration is very similar to a conventional design with the output voltage referenced to the input supply voltage. For SEPIC, the output is referenced to ground and the inductor is split into two parts. One of the inductors (L2) takes LED current as the average current and the other (L1) takes input current as the average current.

Use the following equations (Equations 13–16) to calculate the average inductor currents ( $I_{L1AVG}$ ,  $I_{L2AVG}$ ) and peak inductor currents ( $I_{L1P}$ ,  $I_{L2P}$ ) in amperes.

**Equation 13:**

$$I_{L1AVG} = \frac{I_{LED} \times D_{MAX} \times 1.1}{1 - D_{MAX}}$$

The factor 1.1 provides a 10% margin to account for the converter losses.

**Equation 14:**

$$I_{L2AVG} = I_{LED}$$

Assuming the peak-to-peak inductor ripple  $\Delta I_L$  is  $\pm 30\%$  of the average inductor current

**Equation 15:**

$$\Delta I_{L1} = I_{L1AVG} \times 0.3 \times 2$$

and:

$$I_{L1P} = I_{L1AVG} + \frac{\Delta I_{L1}}{2}$$

and:

$$\Delta I_{L2} = I_{L2AVG} \times 0.3 \times 0.2$$

and:

$$I_{L2P} = I_{L2AVG} + \frac{\Delta I_{L2}}{2}$$

Calculate the minimum inductance values ( $L1_{MIN}$  and  $L2_{MIN}$ ) in henries with the inductor current ripple set to the



maximum value shown in Equation 16.

**Equation 16:**

$$L1_{MIN} = \frac{(V_{IN\_MIN} - V_{DS} - 0.3) \times D_{MAX}}{f_{SW} \times \Delta I_{L1}}$$

$$L2_{MIN} = \frac{(V_{IN\_MIN} - V_{DS} - 0.3) \times D_{MAX}}{f_{SW} \times \Delta I_{L2}}$$

Choose inductors that have a minimum inductance greater than the calculated  $L1_{MIN}$  and  $L2_{MIN}$ , and current rating greater than  $I_{L1P}$  and  $I_{L2P}$ , respectively. The recommended saturation current limit of the selected inductor is 10% higher than the inductor peak current.

To simplify further calculations, consider L1 and L2 as a single inductor with L1 and L2 connected in parallel. The combined inductance value and current is calculated as shown in Equation 17.

**Equation 17:**

$$L = \frac{L1 \times L2}{L1 + L2}$$

and:

$$I_{LAVG} = I_{L1AVG} + I_{L2AVG}$$

where  $I_{LAVG}$  represents the total average current through both the inductors in the SEPIC configuration. Use these values in the calculations in the following sections.

Select coupling-capacitor  $C_S$  so that the peak-to-peak ripple on it is less than 2% of the minimum input supply voltage. This ensures that the second-order effects created by the series-resonant circuit comprising L1,  $C_S$ , and L2 do not affect the normal operation of the converter. Use Equation 18 to calculate the minimum value of  $C_S$ :

**Equation 18:**

$$C_S = \frac{I_{LED} \times D_{MAX}}{V_{IN\_MIN} \times 0.02 \times f_{SW}}$$

where:

- $C_S$  = Minimum value of the coupling capacitor in farads, and
- 0.02 = 2% ripple factor.

### Slope Compensation and Current-Sense Resistor

The device generates a current ramp for slope compensation. This ramp current is in sync with the switching frequency and starts from zero at the beginning of every clock cycle, rising linearly to reach 50 $\mu$ A at the end of the clock cycle. The slope-compensating resistor ( $R_{SC}$ ) is connected between the CS input and the source of the external switching MOSFET. This adds a programmable ramp voltage to the CS input voltage to provide slope compensation.

Use one of the the following equations (Equation 19 or 20) to calculate the value of  $R_{SC}$ .

**For boost configuration (Equation 19):**

$$R_{SC} = \frac{(V_{LED} - 2 \times V_{IN\_MIN}) \times R_{CS} \times 3}{L_{MIN} \times 50\mu A \times f_{SW} \times 4}$$

**For SEPIC and coupled-inductor configurations (Equation 20):**

$$R_{SC} = \frac{(V_{LED} - V_{IN\_MIN}) \times R_{CS} \times 3}{L_{MIN} \times 50\mu A \times f_{SW} \times 4}$$

where:

- $V_{LED}$  and  $V_{IN\_MIN}$  are in volts,
- $R_{SC}$  and  $R_{CS}$  are in ohms,

- $L_{MIN}$  is in henries, and
- $f_{SW}$  is in hertz.

The value of the switch current-sense resistor ( $R_{CS}$ ) can be calculated using the boost configuration shown in Equation 21.

**Equation 21:**

$$R_{CS} = \frac{4 \times L_{MIN} \times f_{SW} \times 0.39 \times 0.9}{I_{LP} \times 4 \times L_{MIN} \times f_{SW} + D_{MAX} \times (V_{LED} - 2 \times V_{IN\_MIN}) \times 3}$$

For SEPIC and coupled-inductor configurations, use Equation 22.

**Equation 22:**

$$R_{CS} = \frac{4 \times L_{MIN} \times f_{SW} \times 0.39 \times 0.9}{I_{LP} \times 4 \times L_{MIN} \times f_{SW} + D_{MAX} \times (V_{LED} - V_{IN\_MIN}) \times 3}$$

where 0.39 is the minimum value of the peak current-sense threshold. The current-sense threshold also includes the slope-compensation component. The minimum current-sense threshold of 0.39 is multiplied by 0.9 to take tolerances into account.

### Output Capacitor Selection

For all three converter topologies, the output capacitor supplies the load current when the main switch is on. The function of the output capacitor is to reduce the converter output ripple to acceptable levels. The entire output-voltage ripple appears across constant-current sink outputs because the LED-string voltages are stable due to the constant current. For the MAX20446B, limit peak-to-peak output-voltage ripple to 200mV to get stable output current.

Use the following equation to calculate the minimum capacitor value:

$$C_{OUT(MIN)} = \frac{I_{LED} \times D_{MAX}}{0.2 \times f_{SW}}$$

The ESR, ESL, and bulk capacitance of the output capacitor contribute to the output ripple. In most applications, using low-ESR ceramic capacitors can dramatically reduce the output ESR and ESL effects. To reduce the ESL and ESR effects, connect multiple ceramic capacitors in parallel to achieve the required bulk capacitance. To minimize audible noise during PWM dimming, the amount of ceramic capacitors on the output are usually minimized. In this case, an additional electrolytic or aluminum organic polymer capacitor provides most of the bulk capacitance.

### Rectifier Diode Selection

Using a Schottky rectifier diode produces less forward drop and puts the least burden on the MOSFET during reverse recovery. A diode with considerable reverse-recovery time increases the MOSFET switching loss. Select a Schottky diode with a voltage rating 20% higher than the maximum boost-converter output voltage and current rating greater than  $I_{LED}$ .

### Feedback Compensation

During normal operation, the feedback control loop regulates the minimum OUT\_ voltage to fall within the window comparator limits of 0.6V and 0.85V when LED string currents are enabled during PWM dimming. When LED currents are off during PWM dimming, the control loop turns off the converter and stores the steady-state condition in the form of capacitor voltages, mainly the output-filter-capacitor voltage and the compensation-capacitor voltage.

The switching converter small-signal-transfer function has a right-half plane (RHP) zero in the boost configuration if the inductor current is in continuous-conduction mode. The RHP zero adds a 20dB/decade gain together with a 90-degree phase lag, which is difficult to compensate.

The worst-case RHP zero frequency ( $f_{ZRHP}$ ) is calculated for boost configuration as shown in Equation 23.

**Equation 23:**

$$f_{ZRHP} = \frac{V_{LED} \times (1 - D_{MAX})^2}{2 \times \pi \times L \times I_{LED}}$$

For the SEPIC and coupled-inductor configurations, see Equation 24.

**Equation 24:**

$$f_{ZRHP} = \frac{V_{LED} \times (1 - D_{MAX})^2}{2 \times \pi \times L \times I_{LED} \times D_{MAX}}$$

The standard way to avoid this zero is to roll off the loop gain to 0dB at a frequency less than 1/5 of the RHP zero frequency with a -20dB/decade slope.

The switching converter small-signal transfer function also has an output pole. The effective output impedance, together with the output filter capacitance, determines the output pole frequency ( $f_{P1}$ ) that is calculated for the boost configuration, as shown in Equation 25.

**Equation 25:**

$$f_{P1} = \frac{I_{LED}}{\pi \times V_{LED} \times C_{OUT}}$$

For SEPIC and coupled-inductor use Equation 26.

**Equation 26:**

$$f_{P1} = \frac{I_{LED} \times D_{MAX}}{\pi \times V_{LED} \times C_{OUT}}$$

Compensation components,  $R_{COMP}$  and  $C_{COMP}$ , perform two functions.  $C_{COMP}$  introduces a low-frequency pole that presents a -20dB/decade slope to the loop gain.  $R_{COMP}$  flattens the gain of the error amplifier for frequencies above the zero formed by  $R_{COMP}$  and  $C_{COMP}$ . For compensation, this zero is placed at  $f_{P1}$  to provide a -20dB/decade slope for frequencies above  $f_{P1}$  to the combined modulator and compensator response.

The value of  $R_{COMP}$ , needed to fix the total loop gain at  $f_{P1}$  so that the total loop gain crosses 0dB with -20dB/decade slope at 1/5 the RHP zero frequency, is calculated as shown in Equation 27.

**Equation 27 (for boost configuration):**

$$R_{COMP} = \frac{f_{ZRHP} \times R_{CS} \times I_{LED} \times A_{OVP}}{5 \times f_{P1} \times GM_{COMP} \times V_{LED} \times (1 - D_{MAX})}$$

**Equation 28 (for SEPIC and coupled-inductor buck-boost configurations):**

$$R_{COMP} = \frac{f_{ZRHP} \times R_{CS} \times I_{LED} \times A_{OVP} \times D_{MAX}}{5 \times f_{P1} \times GM_{COMP} \times V_{LED} \times (1 - D_{MAX})}$$

where:

- $R_{COMP}$  = Compensation resistor in ohms,
- $A_{OVP}$  = BSTMON resistor-divider gain (a value  $\ll 1$ ),
- $R_{CS}$  = Current-sense resistor in ohms, and
- $GM_{COMP}$  = Transconductance of the error amplifier (700 $\mu$ S).

The value of  $C_{COMP}$  is calculated as shown in Equation 29.

**Equation 29:**

$$C_{COMP} = \frac{1}{2 \times \pi \times f_{Z1} \times R_{COMP}}$$

where  $f_{Z1}$  is the compensation zero placed at 1/5 the crossover frequency, which is, in turn, set at 1/5 the  $f_{ZRHP}$ . If the output capacitors do not have low ESR, the ESR zero frequency could fall below the 0dB crossover frequency. An additional pole may be required to cancel out this pole placed at the same frequency. This can be added by connecting

a capacitor from the COMP pin directly to GND with a value shown in Equation 30.

**Equation 30:**

$$GM_{COMP} \times R_{ESR} \times C_{OUT}$$

where  $R_{ESR}$  is the capacitor ESR value and  $C_{OUT}$  is the output-capacitor value.

### External Disconnect-MOSFET Selection

An external pMOSFET can be used to disconnect the boost output from the battery in the event of an output overload or short condition. In the case of the SEPIC or buck-boost, this protection is not necessary so there is no need for the pMOSFET. Connect the PGATE pin to ground in the case of the SEPIC and buck-boost. If it is necessary to have an output short protection for the boost even at power-up, then the current through the pMOSFET (see the [Typical Application Circuits](#)) has to be sensed. Once the current-sense voltage exceeds a certain threshold, it should limit the input current to the programmed threshold. This threshold should be set at a sufficiently high level so it never trips at startup or under normal operating conditions. Check the safe operating area (SOA) of the pMOSFET so the current-limit trip threshold and voltage on the MOSFET do not exceed the limits of the SOA curve of the pMOSFET at the highest operating temperature.

### V<sub>OUT</sub> to OUT\_ Bleed Resistors

The OUT\_ pins have a leakage specification of 12μA (max) in cases where all OUT\_ pins are shorted to 48V (see I<sub>OUTLEAK</sub> in [Electrical Characteristics](#)). This leakage current is dependent on the OUT\_ voltage and is higher at higher voltages. Therefore, in cases where large numbers of LEDs are connected in series, a 100kΩ (or larger) bleed resistor can be placed in parallel with the LED string to prevent the OUT\_ leakage current from very dimly illuminating the LEDs, even when the DIM signal is low (see resistors R8–R11 in [Typical Application Circuits](#)).

### Thermal Considerations

The on-chip power dissipation of the MAX20446B comprises two main factors:

- Current-sink power loss:  $1.1V \times I_{LED}$
- Device operating current power loss:  $V_{IN} \times 15mA$ .

Calculate the total power dissipation by adding the two values calculated above. The junction temperature at the maximum ambient temperature can then be calculated using Equation 31.

**Equation 31:**

$$T_J = T_A + P_{TOT} \times \theta_{JA}$$

where  $T_A$  is the ambient temperature and  $\theta_{JA}$  is the junction-to-ambient thermal resistance of the package (36°C/W on a four-layer board). Ensure that the junction temperature does not exceed 150°C.

The general formula for total power dissipation is shown in Equation 32.

**Equation 32:**

$$P_{TOT} = V_{OUT(MAX)} \times I_{LED} + V_{IN} \times I_Q$$

As an example, consider an application with an operating voltage of 14V and a total output current of 600mA. The total power dissipation is shown in Equation 33.

**Equation 33:**

$$P_{TOT} = 1.1 \times 0.6 + 14 \times 0.015 = 0.87W$$

The maximum junction temperature at an ambient temperature of 85°C is shown in Equation 34.

**Equation 34:**

$$T_J = 85 + 0.87 \times 36 = 116 \text{ } ^\circ\text{C}$$

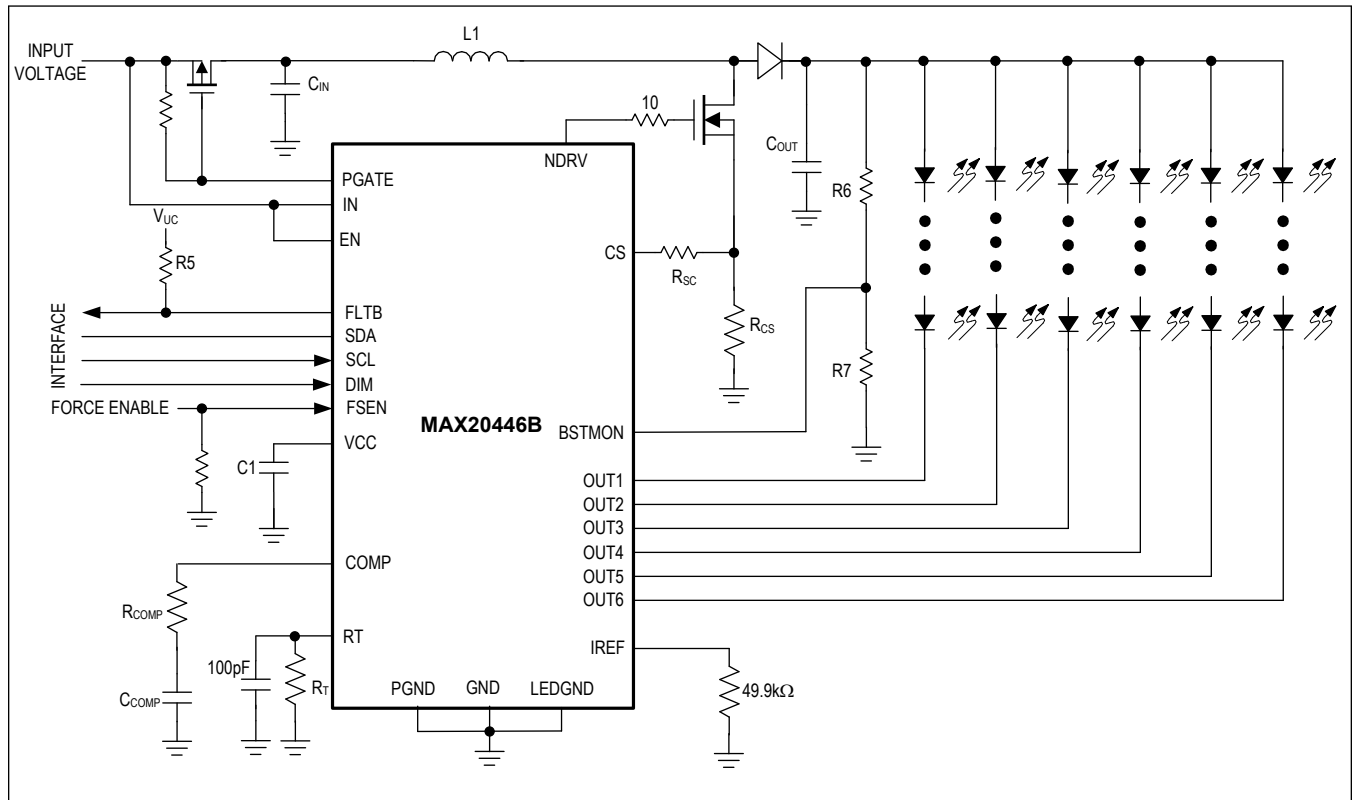
### PCB Layout Considerations

LED driver circuits based on the MAX20446B use a high-frequency switching converter to generate the voltage for LED strings. Take proper care while laying out the circuit to ensure correct operation. The switching-converter portion of the circuit has nodes with very fast voltage changes that could lead to undesirable effects on the sensitive parts of the circuit. Follow the guidelines below to reduce noise as much as possible:

- Connect the bypass capacitor on  $V_{CC}$  as close as possible to the device and connect the capacitor ground to the analog ground plane using vias close to the capacitor terminal. Connect the GND of the device to the analog ground plane using a via close to GND. Lay the analog ground plane on the inner layer, preferably next to the top layer. Use the analog ground plane to cover the entire area under critical signal components for the power converter.
- Have a power-ground plane for the switching-converter power circuit under the power components (i.e., input filter capacitor, output filter capacitor, inductor, MOSFET, rectifier diode, and current-sense resistor). Connect PGND to the power-ground plane closest to PGND. Connect all other ground connections to the power ground plane using vias close to the terminals.
- There are two loops in the power circuit that carry high-frequency switching currents. One loop is when the MOSFET is on (from the input filter capacitor positive terminal, through the inductor, the internal MOSFET and the current-sense resistor, to the input capacitor negative terminal). The other loop is when the MOSFET is off (from the input capacitor positive terminal, through the inductor, the rectifier diode, output filter capacitor, to the input capacitor negative terminal). Analyze these two loops and make the loop areas as small as possible. Wherever possible, have a return path on the power ground plane for the switching currents on the top layer copper traces, or through power components. This reduces the loop area considerably and provides a low-inductance path for the switching currents. Reducing the loop area also reduces radiation during switching.
- Connect the power-ground plane for the constant-current LED driver portion of the circuit to LEDGND as close as possible to the device. Connect GND to PGND at the same point.
- Add a small bypass capacitor (22pF to 47pF) to the BSTMON input. Place the capacitor as close as possible to the pin to suppress high-frequency noise.
- Boost output voltage for the LED strings should be taken directly from the output capacitors and not from the boost diode anode.
- Input and output capacitors need good grounding with wide traces and multiple vias to the ground plane.
- Refer to the MAX20446B evaluation kit (EV kit) data sheet for an example layout.

Typical Application Circuits

MAX20446B Applications Circuit



Ordering Information

PART	TEMP RANGE	PIN-PACKAGE	FEATURES
MAX20446BATG/V+	-40 to +125°C	24 TQFN	Base I <sup>2</sup> C addresses
MAX20446BATGA/V+*	-40 to +125°C	24 TQFN	Alternative I <sup>2</sup> C addresses
MAX20446BATG/VY+	-40 to +125°C	24 SWTQFN	Base I <sup>2</sup> C addresses
MAX20446BATGA/VY+*	-40 to +125°C	24 SWTQFN	Alternative I <sup>2</sup> C addresses

V denotes an automotive-qualified part.

+Denotes a lead(Pb)-free/RoHS-compliant package.

SW = Side-wettable package

T Denotes Tape and reel.

\*Future product - contact factory for availability.